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(54) **ACTIVE MATRIX ELECTROLUMINESCENT DISPLAY DEVICES AND THEIR MANUFACTURE**

ELEKTROLUMINESZIERENDE ANZEIGEVORRICHTUNGEN MIT AKTIVER MATRIX UND DEREN
HERSTELLUNGSVERFAHREN

DISPOSITIFS D'AFFICHAGE ELECTROLUMINESCENTS A MATRICE ACTIVE ET LEUR
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Description

[0001] This invention relates to active-matrix electroluminescent display devices, particularly but not exclusively using light-emitting diodes of semiconducting conjugated polymer or other organic semiconductor materials. The invention also relates to methods of manufacturing such devices.

[0002] Such active-matrix electroluminescent display devices are known, comprising an array of pixels that is present on a circuit substrate, wherein each pixel comprises a current-driven electroluminescent element, typically of organic semiconductor material.

[0003] In many such arrays, physical barriers of insulating material are present between neighbouring pixels in at least one direction of the array. Examples of such barriers are given in published United Kingdom patent application GB-A-2347017, published PCT patent application WO-A1-99/43031, published European patent applications EP-A-0 895 219, EP-A-1 096 568, and EP-A-1 102 317.

[0004] Such barriers are sometimes termed "walls", "partitions", "banks", "ribs", "separators", or "dams", for example. As can be seen from the cited references, they may serve several functions. They may be used in manufacture to define electroluminescent layers and/or electrode layers of the individual pixels and/or of columns of pixels. Thus, for example, the barriers prevent pixel overflow of conjugate polymer materials that may be ink-jet printed for red, green and blue pixels of a colour display or spin-coated for a monochrome display. The barriers in the manufactured device can provide a well-defined optical separation of pixels. They may also carry or comprise conductive material (such as upper electrode material of the electroluminescent element), as auxiliary wiring for reducing the resistance of (and hence the voltage drops across) the common upper electrode of the electroluminescent elements.

[0005] Each electroluminescent element of an active-matrix display device is connected in series with a drive element (typically a thin-film transistor, hereafter termed "TFT") between two voltage supply lines of the array. These two supply lines are typically a power supply line and a ground line (also termed "return line"). Light emission from the electroluminescent element, typically a LED, is controlled by the current flow therethrough, as altered by its respective drive element TFT. The supply line to which the electroluminescent elements are connected by their series drive elements may be termed the "drive supply line" or "drive line" or "current drive line" of the pixels. Voltage drops along these two supply lines can result in incorrect drive currents for individual pixels. This can lead to a decrease in emission intensity (i.e. fading of the image) from pixels in the centre of the display. Indeed, with large-area displays, the effect may be so bad that no emission occurs at the centre, so limiting the acceptable display size.

[0006] Several measures have been proposed in order

to reduce such voltage drops and/or their effects for a row of pixels. Thus, it is known from published United States patent application US-A1-2001/0007413 to reduce voltage drops along the line by tapering the width of the line. Published PCT patent applications WO-A1-01/01383 and WO-A1-01/01384 adopt a different approach in which error values are generated to correct the drive signals for each pixel.

[0007] European Patent Application Publication Number EP 0862156 A1 discloses a matrix type display device having a structure in which an optical material is selectively arranged at predetermined positions on a display substrate.

[0008] It is an aim of the present invention to reduce such voltage drops along the drive supply line, and to do so in a manner that does not significantly complicate the device structure, its layout and its electronics.

[0009] According to one aspect of the present invention, there is provided an active-matrix electroluminescent display device with the features of Claim 1.

[0010] In accordance with the invention, the physical barriers between pixels are partly and/or predominantly of electrically-conductive material (typically metal) that is insulated from the electroluminescent elements and that provides at least a part of the drive supply line. This conductive barrier material may form a conductive core of the barrier. It is connected into the circuit substrate, to electrode connections for the respective drive elements, via contact windows (hereinafter termed "vias") between the pixel barriers and the drive elements in the substrate. Thus, the problem of line resistance and associated voltage drop is transferred from within the circuit substrate (where it is severely constrained) to the much freer environment of the pixel barriers on the substrate (where the conductive barrier material can provide much lower resistance).

[0011] By this means, the electrical resistance along the drive supply line (and consequential voltage drops) can be significantly reduced, as compared with a conductor layer within the circuit substrate, for example a thin-film electrode line of the drive element. Thus, along this drive line, the conductive barrier material has a cross-sectional area that is typically larger (for example, at least twice as large as, or even at least an order of magnitude larger) than that of a thin conductor layer in the circuit substrate. As such, the resistance (even of long lines) can be low, and very large electroluminescent displays can be constructed in accordance with the invention. Even with smaller displays, the image quality can be improved by use of the conductive barrier material in accordance with the present invention.

[0012] By providing one via per pixel, continuous barrier lines of conductive material on the circuit substrate can be used to replace the drive lines that were previously incorporated within the circuit substrate. This permits an increase in pixel aperture. The conductive barrier line itself may simply overlap with a column or row conductor line of the array. Alternatively, lines (or individual lengths)

of the conductive barrier material may be used to back-up corresponding lengths of a drive line of the circuit substrate. This alternative provides greater choice in the number and location of the vias.

[0013] The design of such a device structure in accordance with the invention may also be optimised to include a smoothing capacitor between the two voltage supply lines of the electroluminescent element. The insulation of the conductive barrier material from the electroluminescent elements can form a capacitor dielectric of this smoothing capacitor. This insulation may be in the form of a coating on the sides and top of the conductive barrier material. Typically, the said further supply line (for the upper electrode of the electroluminescent element) may extend on this insulating coating over the top of the conductive barrier material. Thus, a smoothing capacitor for the power supply can be readily realized between the drive line that comprises the conductive barrier material and the further supply line that comprises upper electrodes of the electroluminescent elements.

[0014] It is advantageous for the physical barriers to extend as a network of conductive barrier material between pixels in both row and column directions of the array. Such a network of conductive barrier material can serve to reduce resistance between drive line areas across the array. It can also provide a design option in determining the capacitance value of the smoothing capacitor for the power supply to the electroluminescent elements.

[0015] However, the physical barriers may extend between pixels in just one direction of the array, for example in a column or row direction. In this case, additional insulated barriers of conductive barrier material may be provided in the transverse direction for a different purpose, for example to back-up a row or column line. These additional insulated barriers may even be constructed to form an additional component, for example a holding capacitor at each pixel.

[0016] According to another aspect of the present invention, there are also provided advantageous methods of manufacturing such an active-matrix electroluminescent display device in accordance with the first aspect. The method may include the steps of:

- (a) opening contact windows in the intermediate insulating layer on the circuit substrate to expose electrode connections for respective drive elements of at least some of the pixels;
- (b) forming the physical barriers from electrically-conductive material deposited on the insulating layer at least in the contact windows of the electrode connections
- (c) providing the electroluminescent elements in the pixel areas in between the physical barriers, wherein the conductive barrier material is provided by depositing electrically-conductive material at least for connection at the contact windows of the intermediate insulating layer

(d) opening contact windows in the intermediate insulating layer in the pixel areas between the physical barriers and wherein the electroluminescent elements are provided in the further windows and have a lower electrode connection to the drive element.

[0017] Various processes may advantageously be used to deposit and form the barrier material(s) and to insulate the conductive barrier material.

[0018] Various advantageous features and feature-combinations in accordance with the present invention are set out in the appended Claims. These and others are illustrated in embodiments of the invention that are now described, by way of example, with reference to the accompanying diagrammatic drawings, in which:

Figure 1 is a cross-sectional view of part of a pixel array and circuit substrate of an active-matrix electroluminescent display device (that has conductive barriers forming at least part of a drive line) as one particular embodiment of the invention;

Figure 2 is a plan view of four pixel areas (showing a specific example of layout features for the conductive barriers of such a device in accordance with the invention), the cross-section of Figure 1 being taken on the line I-I of Figure 2;

Figure 3 is circuit diagram for four such pixel areas of such a device in accordance with the invention;

Figure 4 is a cross-sectional view, through a holding capacitor, of part of a pixel array and circuit substrate in the same and/or another embodiment of the active-matrix display device in accordance with the invention;

Figure 5 is a plan view similar to Figure 2, but showing an example of a network layout feature for the conductive barriers of the drive line of a further device embodiment in accordance with the invention;

Figures 6 and 7 are plan views similar to Figure 2, showing two examples of different layout features for the conductive barriers of other devices in accordance with the invention, with back-up for row conductors as well as the drive line;

Figures 8 and 9 are circuit diagrams for two modified pixel-drive configurations of a pixel area of two further devices in accordance with the invention;

Figures 10 to 12 are sectional views of a device part such as that of Figure 1 at stages in its manufacture with one particular embodiment in accordance with the invention;

Figure 13 is a sectional view a device part at the Figure 12 stage, illustrating a modification in the insulation of the conductive barriers of the drive line that is also in accordance with the present invention; Figure 14 is a sectional view of another embodiment of a conductive barrier construction using a metal coating to form at least part of the drive line in accordance with the invention;

Figure 15 is a cross-sectional view through side-by-

side barriers, each with conductive barrier material that may be used in different embodiments of the invention;

Figure 16 is a plan view of transverse multiple barrier layout features that may be used in different embodiments of the invention; and

Figure 17 is a cross-sectional view of a barrier embodiment with multiple conductive parts that may be used in different embodiments of the invention.

[0019] It should be noted that all the Figures are diagrammatic. Relative dimensions and proportions of parts of these Figures have been shown exaggerated or reduced in size, for the sake of clarity and convenience in the drawings. The same reference signs are generally used to refer to corresponding or similar features in modified and different embodiments.

Embodiments of Figures 1 to 4

[0020] The active-matrix electroluminescent display device of Figure 1 comprises an array of pixels 200 on a circuit substrate 100. Each pixel 200 comprises a current-driven electroluminescent element 25 (21,22,23) that is connected to a supply line 140,240 by a current-controlling series drive element T1 (1-5) in the circuit substrate 100. This series element T1, typically a TFT, controls the current through the electroluminescent element 25 (21,22,23). As described below, the display can be very large in area due to the construction of these current drive lines 140,240 using conductive barrier material 240 in accordance with the present invention. Apart from this construction of the drive supply lines 140,240 in accordance with the present invention, the display may be constructed using known device technologies and circuit technologies, for example as in the background references cited hereinbefore.

[0021] Thus, the electroluminescent element 25 typically comprises a light-emitting diode (LED) of organic semiconductor material 22 between a lower electrode 21 and an upper electrode 23. In a preferred particular embodiment, semiconducting conjugated polymers may be used for the electroluminescent material 22. For a LED that emits its light 250 through the substrate 100, the lower electrode 21 may be an anode of indium tin oxide (ITO), and the upper electrode 23 may be a cathode comprising, for example, calcium and aluminium. Figure 1 illustrates a LED construction in which the lower electrode 21 is formed as a thin film in the circuit substrate 100. The subsequently-deposited organic semiconductor material 22 contacts this thin-film electrode layer 21 at a window 12a in a planar insulating layer 12 (for example of silicon nitride) that extends over the thin-film structure of the substrate 100.

[0022] As illustrated in Figures 1 and 3, the LED 25 and its drive element T1 are connected in series between a pair of voltage supply lines 140,240 and 230. The line 140,240 (to/from which the drive elements T1 control the

LED connection, and hence the current flow) is termed the drive line. The other line 230 is connected directly to the LED 25. Thus, in the particular embodiment of Figure 1, the line 230 is formed as a common extension of the upper electrodes 23 of the pixels 200. In the circuit configuration of Figure 3, the line 230 is grounded and so forms a return line, whereas voltage Vdd is applied to the line 140,240 as a power supply line.

[0023] The series drive element T1 typically comprises a TFT that is formed as part of a thin-film circuit within the substrate 100. The substrate 100 may have an insulating glass base 10 on which an insulating surface-buffer layer 11, for example, of silicon dioxide is deposited. The thin-film circuitry is built up on the layer 11 in known manner. Thus, in addition to TFT T1, the circuit substrate 100 typically includes other drive and matrix addressing circuitry, for example with thin-film elements T2, Ch, 140, 150 and 160 as illustrated in Figure 3. It should be understood that Figure 3 depicts, by way of example, one specific pixel circuit configuration. Other pixel circuit configurations are known for active matrix electroluminescent display devices. It should readily be understood that the present invention may be applied to the pixel barriers of such a device regardless of the specific pixel circuit configuration of the device.

[0024] As illustrated in Figure 3, the pixel circuit comprises addressing TFTs T2 between transverse sets of row (addressing) conductors 150 and column (data) conductors 160, all of which are formed in the substrate 100. Each row of pixels is addressed in turn in a frame period by means of a selection signal that is applied to the relevant row conductor 150 (and hence to the gate of the addressing TFTs T2 of the pixels of that row). This signal turns on the addressing TFT T2, so loading the pixels of that row with respective data signals from the column conductors 160. These data signals are applied to the gate of the individual drive TFT T1 of the respective pixel. In order to hold the resulting conductive state of the drive TFT T1, this data signal is maintained on its gate 5 by a holding capacitor Ch that is coupled between this gate 5 and the drive line 140,240. Thus, the drive current through the LED 25 of each pixel 200 is controlled by the driving TFT T1 based on a drive signal applied during the preceding address period and stored as a voltage on the associated capacitor Ch. In the specific example of Figure 3, T1 is shown as a P-channel TFT, whereas T2 is shown as an N-channel TFT.

[0025] This circuitry can be constructed with known thin-film technology.

[0026] Figure 1 illustrates the P-channel TFT T1 comprising: an active semiconductor layer 1 (typically of polysilicon); a gate dielectric layer 2 (typically of silicon dioxide); a gate electrode 5 (typically of aluminium or polysilicon); and metal electrodes 3 and 4 (typically of aluminium) which contact P-type doped source and drain regions of the semiconductor layer 1 through windows (vias) in the over-lying insulating layer(s) 2 and 8. Extensions of these metal electrodes 3 and 4 at the upper level

form an interconnection between TFT electrode 3 and the lower electrode 21 of the LED and form at least a connection area 140 of the drive line 140,240. In a particular layout embodiment (such as that of Figure 2), this extension of the metal electrodes 4 of a row may form a continuous line 140 for that row. Figure 1 illustrates also a section through the address lines 150, which may be, for example, of aluminium or polysilicon and which may be formed from the same layer as the TFT gates 5.

[0027] The holding capacitor Ch may be formed similarly, in known manner, as a thin-film structure inside the circuit substrate 100. Thus, Figure 4 illustrates such a capacitor Ch that comprises a thin-film conductor plate 155 on a thin-film dielectric 2 on a thin-film conductive plate 105.

[0028] As in known devices, the device(s) of Figures 1 to 4 in accordance with the present invention include physical barriers 210, between at least some of the neighbouring pixels in at least one direction of the array. These barriers 210 may also be termed "walls", "partitions", "banks", "ribs", "separators", or "dams", for example. Depending on the particular device embodiment and its manufacture, they may be used in known manner, for example:

- to separate and prevent overflow of a polymer solution between the respective areas of the individual pixels 200 and/or columns of pixels 200, during the provision of semiconducting polymer layers 22;
- to provide a self-patterning ability on the substrate surface in the definition of the semiconducting polymer or other electroluminescent layers 22 for the individual pixels 200 and/or for columns of pixels 200 (and possibly even a self-separation of individual electrodes for the pixels, for example an individual bottom layer of the upper electrodes 23);
- to act as a spacer for a mask over the substrate surface during the deposition of at least an organic semiconductor material 22 and/or electrode material;
- to form opaque barriers 210 for a well-defined optical separation of the pixels 200 in the array, when light 250 is emitted through the top (instead of, or as well as, the bottom substrate 100).

[0029] Whatever their specific use in these known ways, the physical barriers 210 in an embodiment of the present invention are constructed and used in a special manner. Thus, the pixel barriers 210 which are provided in accordance with the present invention are predominantly of electrically-conductive material 240 that is insulated from the LEDs 25 and that provides at least a part of the drive line 140,240. The barriers 210 comprise a bulk or core of conductive material 240 that is preferably metal (for very low resistivity, for example aluminium or copper or nickel or silver). Contact windows 12b are present in the intermediate insulating layer 12 between the barriers 210 and the substrate circuitry. The conduc-

tive barrier material 240 is connected to the electrode connections 4, 140 for respective drive elements T1 of at least some of the pixels 200 at the vias provided by these windows 12b. As illustrated in Figure 1, its source and drain electrodes connect the main current path of the current-controlling drive TFT T1 between the conductive barrier material 240 of the drive line and the lower electrode 21 of the LED 25.

[0030] These drive line connections (and/or composite nature of the drive line 140,240) with the conductive barrier material 240 serve to decrease voltage drops along the line 140,240 as it extends across the array. As a result, the displays can be made very large in area, for example at least a metre (i.e. over 30 inches) wide. Before the advent of the present invention, it was difficult (perhaps even impossible) to make very large active-matrix electroluminescent displays due to voltage errors along the drive lines when conducting current in the conducting light-emitting state. However, the present invention can also be used with advantage in smaller displays, to improve their image quality.

[0031] Thus, along the line 140,240, the conductive barrier material 240 has a cross-sectional area that is at least twice (possibly even an order of magnitude) larger than that of the conductor layer that provides the electrode connection 4, 140 to the drive element T1. Typically, the conductive barrier material 240 may have a thickness Z that is a factor of two or more (for example at least five times) larger than the thickness z of this conductor layer 140 in the circuit substrate 100. In a specific example, Z may be between 2 μ m and 5 μ m as compared with 0.5 μ m or less for z. Typically, the conductive barrier material 240 may have a line width Y that is the same width (or even at least twice as large) as the line width y of the conductor layer 140. In a specific example, Y may be 20 μ m as compared with 10 μ m for y.

[0032] It is important to note a further feature that is present in this device structure, for reducing the effect of voltage variations on the supply lines 230 and 140,240. Thus, a smoothing capacitor Cs is formed between the drive line 140,240 (that comprises the conductive barrier material 240) and the further supply line 230 (that is associated with the upper electrodes 23 of the LEDs 25). As illustrated in Figure 1, the sides and top of the conductive barrier material 240 are coated with an insulating layer 40. The thickness and dielectric properties of this insulating coating 40 can be chosen to form a capacitor dielectric of the smoothing capacitor Cs. The other plate of the capacitor Cs is formed by the supply line 230 (comprising and/or connecting the LED upper electrodes 23), that extends on this insulating coating 40 over the top of the conductive barrier material 240. Typically, this insulating coating 40 may be of silicon dioxide or nitride or of aluminium oxide and have a thickness in the range of 10nm (nanometres) to 0.5 μ m (micrometres).

Layout Embodiment of Figure 2

[0033] In the specific layout example of Figure 2, the extensions of the TFT electrodes 4 of a pixel row form a continuous line 140 for that row. This line 140 extends parallel to barriers 210(240,40). These barriers 210 (shown in broken outline in Figure 2) extend parallel to the address (row) conductors 150 of the substrate 100.

[0034] As illustrated in Figure 2, when the barriers 210 (240,40) extend parallel to one or more lines (such as lines 140 and 150 in Figure 2), these lines may be fully overlapped by the barriers 120. Indeed the width Y of the barriers 210 (240,40) of Figure 2 is so large as to overlap both the lines 140 and 150. Nonetheless, the thin-film pixel circuitry of Figure 3 may encroach somewhat into the pixel area as illustrated by the hatched circuit area 120.

[0035] The conductive barrier material 240 is connected at the vias 12b to a node of the drive element T1 and one plate of the holding capacitor Ch. Figure 2 illustrates an embodiment in which each pixel 200 has a respective via 12b between the conductive barrier material 240 and the electrode connection 140,4 for the respective drive element T1 of the pixel.

[0036] In the Figures 1 and 2 illustration, at least most of the drive element T1 is located below the conductive barrier material 240. The width Y and length of the conductive barrier material 240 permits at least most of the holding capacitor Ch to be located below the conductive barrier material 240, for example in the Figures 2 and 4 illustration. The drive element T1 of each pixel may have its respective electrode 4 located at a/the via 12b and/or the respective capacitor plate 155 may be located at a/the via 12b.

[0037] Each barrier 210(240,40) of the Figure 2 layout may extend across the whole array. Thus, it may form a continuous supply line of the conductive barrier material 240 that is connected to electrode connections 4,140 for the respective drive elements T1 of the respective pixels 200. In this case, it may parallel the line 140. However, if the line resistance of the conductive barrier material 240 is itself sufficiently low, it can simply replace the substrate conductor line 140. Thus, it is not necessary for the extension 140 of the TFT electrodes 4 to form a continuous line, and an increase in pixel aperture can be achieved by omitting lengths of the line 140 in most of the pixel area.

Layout Embodiment of Figure 5

[0038] The specific layout example of Figure 5 is a modification of that of Figure 2. In this modification, the barriers 210(240,40) extend in both row and column directions of the array. Thus, in this particular embodiment, the barriers 210(240,40) are interconnected between pixels to form a network of conductive barrier material 240 in both the row and column directions.

[0039] There are several potential advantages in

adopting such a network of the conductive barrier material 240, as compared with separate parallel lines. Thus, the network of conductive barrier material 240 is effectively an apertured sheet conductor, in which the resistance between any two points is lower than in the Figure 2 layout. It can also provide a design option in determining the capacitance value of the smoothing capacitor Cs for the power supply to the LEDs 25.

Layout Embodiments of Figures 6 and 7

[0040] Reduction of voltage drops along the addressing (row) lines 150 is also desirable in large arrays. Figures 6 and 7 illustrate how additional barriers 210c that are of the same construction as barriers 210 (i.e. predominantly of the conductive barrier material 240) may be used for this purpose. The specific layout examples of Figures 6 and 7 are given as modifications of that of Figure 2. In each case, the pixel barriers 210 that provide at least the low-resistance part 240 of the drive line 140,240 are also retained in the device.

[0041] The additional barriers 210c of conductive material 240 extend parallel to the row conductors 150, as shown in Figures 6 and 7. They are connected at additional vias 12c in the intermediate insulating layer 12 to the row conductors 150 in the circuit substrate 100 to reduce voltage drops along the row conductors 150. As such, these additional barriers 210c back-up parts of the row lines 150 to reduce their resistance. They are insulated from the barriers 210 that form at least part of the drive line 140,240.

[0042] In the Figure 6 modification, the additional barriers 210c that back-up the row lines 150 extend parallel to the barriers 210 that provide at least the low-resistance part 240 of the drive line 140,240. Thus, these barriers 210 and 210c both extend in the same direction between pixels 200 of the array.

[0043] In the Figure 7 modification, the barriers 210 extend parallel to the column conductors 160. They provide a continuous low-resistance drive line 240 replacing the line 140, as in Figure 8. Such a modification could be made to the display devices of Figures 1 to 4 without including additional barriers 210c for the row lines 150. However, Figure 7 illustrates a layout that includes the additional barriers 210c to back-up the row lines 150. In this embodiment, the additional barriers 210c extend transverse to the barriers 210 of the drive line 140,240. Thus, barriers 210 extend in one direction of the array, and barriers 210c extend in the transverse direction. The barriers 120 and 120c thus form a network between pixels of the array. However, unlike Figure 5, the conductive barrier material 240 in the transverse direction (barriers 210c) of the network is insulated from that in the other direction (barriers 210).

Circuit Embodiment of Figure 8

[0044] As mentioned above with respect to Figure 2,

the extensions 140 of the TFT electrodes 4 need not form a continuous line, when the barrier 210(240,40) itself provides a continuous line of the conductive barrier material 240. Thus, the continuous line of the conductive barrier material 240 may replace the line 140 of the circuit substrate 100. Such a scenario is illustrated in the circuit diagram of Figure 8. The continuous line of the conductive barrier material 240 is connected to the electrode connections 140 for the respective drive element T1 and holding capacitor Ch of all the respective pixels 200 of a row. Each of the pixels 200 is provided with a respective via 12b between its electrode connection 140 and the conductive barrier material 240.

Circuit Embodiment of Figure 9

[0045] In the embodiments so far described with reference to Figures 1 to 8, the line 230 is grounded and so forms a return line, whereas voltage Vdd is applied to the line 140,240 as a power supply line. Figure 9 illustrates an alternative configuration in which line 140,240 (that comprises the conductive barrier material 240) is grounded and so forms the return line. In this case, the drive voltage Vdd is applied to line 230 (that comprises or is connected to the upper electrode 23 of the LED 25). Thus, the line 230 is now the power supply line.

[0046] Furthermore, the upper electrode 23 of the LED 25 is now of anode material, whereas the lower electrode 23 is now formed of cathode material. Such a display may, for example, emit its light 250 through the top surface rather than through the substrate 100. The light-emitting layer 22 may be of, for example, molecular (small molecule) organic semiconductor material, or it may be of a semiconducting polymer.

[0047] However, as in the previous embodiments, the conductive barrier material 240 forms part of the drive line, i.e. the line to which the LED 25 is connected via the drive element T1

Process Embodiment of Figures 10 to 12

[0048] Apart from the construction of the drive lines 140,240, an active-matrix electroluminescent display device in accordance with the present invention may be constructed using known device technologies and circuit technologies, for example as in the cited background references.

[0049] Figures 10 to 12 illustrate novel process steps in a particular manufacturing embodiment. The thin-film circuit substrate 100 with its upper planar insulating layer 12 (for example, of silicon nitride) is manufactured in known manner. Contact windows (such as vias 12a, 12b, 12c etc.) are opened in the layer 12 in known manner, for example by photolithographic masking and etching. However, in order to manufacture a device in accordance with the present invention, the pattern of these vias include the vias 12b that expose electrode connections 140,4 of respective drive elements T1 for at least some

of the pixels 200. The resulting structure is illustrated in Figure 10.

[0050] Thereafter electrically-conductive material for the barriers 210 is deposited on the insulating layer 12 at least in its vias 12a, 12b, 12c etc. The desired layout for the barriers 210 (for example, as in Figures 2, 5, 6, or 7) is obtained using known masking techniques. Figure 11 illustrates an embodiment in which at least the bulk 240b of the conductive barrier material (for example, copper or nickel or silver) is deposited by plating. In this case, a thin seed layer 240a of, for example, copper or nickel or silver is first deposited over the insulating layer 12 and its vias 12a, 12b, 12c etc, the barrier layout pattern is defined with a photolithographic mask, and then the bulk 240b of the conductive barrier material is plated to the desired thickness Z. The resulting structure is illustrated in Figure 11.

[0051] Then, using CVD (chemical vapour deposition), insulating material (for example silicon dioxide or silicon nitride) is deposited for the insulating coating 40. The deposited material is left on the sides and top of the conductive barrier material by patterning using known photolithographic masking and etching techniques. The resulting structure is illustrated in Figure 12.

[0052] Thereafter the manufacture is continued in known manner. Thus, for example, conjugate polymer materials may be ink-jet printed or spin-coated for the pixels 200. The barriers 240,40 with their insulating coating 40 can be used in known manner to prevent polymer overflow from the pixel areas in between the physical barriers 240,40. Thereafter the upper electrode material 23, 230 can be deposited.

Modified Process Embodiment of Figure 13

[0053] This embodiment uses an anodisation treatment (instead of deposition) to provide the insulating coating 40 at least at the sides of the barriers 210 adjacent to the pixel areas. Typically, the conductive barrier material 240 may comprise aluminium. The desired layout pattern of the deposited aluminium (for example, as in Figures 2, 5, 6, or 7) can be defined using known photolithographic masking and etching techniques. Figure 13 shows the photolithically-defined etchant-mask 44 retained on the top of the aluminium barrier pattern 240.

[0054] Then, an anodic insulating coating of aluminium oxide is formed on at least the sides of the aluminium barrier material 240 using known anodisation techniques. Thus, no extra mask is needed to define the layout for this coating 40.

[0055] If the mask 44 is removed before this anodisation, the anodic coating is formed at both the sides and top of the aluminium barrier pattern 240. However, Figure 13 illustrates an example in which the mask 44 is retained during this anodisation, so that the anodic coating is formed at only the sides of the aluminium barrier pattern 240. In devices having the supply line 230 extending over the top of the barrier 210(240,40), then the mask 44 of

an insulating polymer or, for example, silicon dioxide or nitride may be retained in the manufactured device.

Alternative Conductive Barrier Embodiment of Figure 14

[0056] In the embodiments so far described, the barriers 210 are shown as being predominantly of conductive material 240. Figure 14 shows a modified embodiment wherein the barrier 210 is predominantly of insulating material 244. In this case, vias 244b are etched or milled through the insulating material 244 to the electrode area 140, 4 of TFT T1 in the circuit substrate 100. A metal coating 240 provides the conductive barrier material that extends on top of the insulating barrier 210 and in the vias 244b therethrough. This metal coating 240 backs up or replaces the thin-film drive supply line 140.

[0057] The circuit substrate 100 can be formed with its planar layer 12 and vias 12a and 12b as described above with reference to Figure 10. The insulating bulk material 244 of the Figure 14 is then formed thereon with its via 244b. Then the metal coating 240 of this barrier 210 may be formed simultaneously with a main part of the upper electrode 23 of the LED 25, in a self-aligned manner. Thus, a layer of metal may be deposited simultaneously for the metal coating 240 and electrode 23 which are separated by a shadow-masking effect of an overhang shape in the side of the barrier 210, as illustrated in Figure 14.

Multi-conductor Barrier Embodiments of Figure 15

[0058] Figure 15 illustrates a composite of two side-by-side barriers 210 and 210x, each comprising a metal core 240, 240x insulated with a respective coating 40, 40x. This side-by-side multi-conductor barrier structure 210, 210x can be designed and used in a variety of ways.

[0059] In one form, for example, the metal cores 240 and 240x may form (or back up) parallel drive and addressing lines 140 and 150 respectively, for example as a cross-section of the side-by-side barrier lines 140 and 150 of Figure 6.

[0060] In another form, for example, one of the barriers 210x may be divided into insulated portions that provide an additional component, for example a capacitor as described below with reference to Figure 17.

Multi-conductor barrier embodiments of Figures 16 and 17

[0061] The Figure 16 embodiment is similar to that of Figure 7, in having insulated barrier lengths 210c that extend transverse to the drive-line barriers 210, 140. These transverse barriers 210c may back up lines 150, as described already with respect to Figure 7. However, they may be constructed and used for other purposes.

[0062] Thus, for example, the transverse barriers 210c may themselves have a multi-conductor structure, such as that of Figure 17. This barrier embodiment comprises

a metal core 240c as the main conductive barrier material that is connected with the circuit element such as 4 or 5 etc. in the substrate 100 and that has an insulating coating 40c on thereon. However the embodiment of Figure 17 additionally comprises a metal coating 240d that is present on the insulating coating 40c, over the top and sides of the core 240c. This metal coating 240d is connected to another circuit element of, for example, the substrate 100 such as element 6, 5, 4, etc.

[0063] This barrier structure of Figure 17 is more versatile than that previously described. It permits the metal core 240c and metal coating 240d to be used for different purposes, for example, to back-up or even replace different lines 140, 150 or 160, so reducing their line resistance. The metal coating 240d may serve as a co-axial shield for the signal on the core line 240c. Alternatively, the metal coating 240d may be localised to specific locations along the barrier 210c where particular connections or components are required, for example at individual pixels or sub-pixels.

[0064] Instead of shielding, this multi-conductor structure 240c, 240d for the barrier 210c might be used to overlap two lines; for example, a back-up or replacement barrier line 140 (including core 240c) with a back-up or replacement barrier line 150 (including coating 240d). In this case, however, the thickness and dielectric properties of the insulating coating 40c need to be chosen to reduce parasitic capacitance and coupling between these lines 140 and 150.

[0065] Of particular importance is an embodiment in which the multi-conductor structure 240c, 240d of Figure 17 is designed to form a capacitor with a capacitor dielectric 40c. Thus, separate and/or insulated lengths of the metal core 240c, insulating coating 40c and metal coating 240d may together form a capacitor connected between the substrate circuit elements 4, 5, etc.

[0066] Such a capacitor may be designed to provide, for example, the individual holding capacitor Ch for each respective pixel 200 which is connected between the supply line 140 (main electrode line 4 of TFT T1) and the gate line 5 of TFT T2 (and main electrode line 3 of TFT T1). Figure 16 illustrates a suitable pixel layout with this holding-capacitor barrier 210c, Ch.

[0067] The Figure 17 capacitor structure (240c, 40c, 240d) of Figure 17 may even be connected between the lines 230 and 240 to form a smoothing capacitor, either instead of or in addition to that provided by the structure 240, 40, 230 in Figure 1, for example.

[0068] In the embodiments described so far, the conductive barrier material 240 is a thick opaque metal, for example, aluminium, copper, nickel or silver. However, other conductive materials 240 may be used, for example a metal silicide or (less advantageously) a degenerately-doped polysilicon both of which may be surface-oxidised to form the insulating coating 40. If transparent barriers 210 are required, then ITO may be used for the conductive barrier material 240.

[0069] From reading the present disclosure, other var-

iations and modifications will be apparent to persons skilled in the art. Such variations and modifications may involve equivalent and other features which are already known in the art (for example in the cited background references) and which may be used instead of or in addition to features already described herein.

[0070] Although Claims have been formulated in this Application to particular combinations of features, it should be understood that the scope of the disclosure of the present invention also includes any novel feature or any novel combination of features disclosed herein either explicitly or implicitly or any generalisation thereof, whether or not it relates to the same invention as presently claimed in any Claim and whether or not it mitigates any or all of the same technical problems as does the present invention.

Claims

1. An active-matrix electroluminescent display device comprising a substrate (100) on which an array of pixels (200) is present with physical barriers (210) between neighbouring pixels in at least one direction of the array, wherein each pixel (200) comprises a current-driven electroluminescent element (25; LED) that is connected to a supply line (140,240) by a series drive element (T1) in the substrate, and wherein the physical barriers are partly of electrically-conductive material (240) that is insulated (40) from the electroluminescent elements (25; LED) and that provides at least a part (240) of the supply line (140,240), which conductive barrier material (240) is connected to respective drive elements (T1) of at least some of the pixels (200) at contact windows (12b) in an intermediate insulating layer (12) between the barriers (210) and the drive elements (T1), and wherein the electroluminescent element (25; LED) has a lower electrode connection (21) to the drive element (T1), **characterised in that** the electroluminescent element (25; LED) is present in a further window (12a) in the intermediate insulating layer (12).
2. A device according to Claim 1, wherein an insulating coating (40) extends on the sides and top of the conductive barrier material (240), and a further supply line (230) comprises upper electrodes (23) of the electroluminescent elements (25; LED) and extends on the insulating coating (40) over the top of the conductive barrier material (240).
3. A device according to Claim 2, wherein the insulating coating (40) forms a capacitor dielectric of a smoothing capacitor (Cs) between the drive supply line (140,240) that comprises the conductive barrier material and the further supply line (230) that comprises the upper electrodes of the electroluminescent ele-

ments.

4. A device according to any one of the preceding Claims, wherein each pixel (200) has a respective contact window (12b) between the conductive barrier material (240) and an electrode connection (4,140) for the respective drive element (T1) of the pixel.
5. A device according to any one of the preceding Claims, wherein the drive element (T1) of each pixel has a respective electrode (4) located at the contact window (12b) where it is connected to the conductive barrier material (240).
6. A device according to any one of Claims 1 to 4, wherein each pixel (200) comprises a holding capacitor (Ch) for holding the drive element (T1) in a given conduction state, and the conductive barrier material (140) is connected at the contact window (12b) to a node of the drive element (T1) and one plate of the holding capacitor (Ch).
7. A device according to Claim 6, wherein the holding capacitors are formed by respective insulated lengths of additional barriers (210c) that extend transverse to the supply-line barriers (201) and that comprise a metal coating (230) on a dielectric coating (40) on a metal core (240).
8. A device according to any one of the preceding Claims, wherein, along the drive supply line (140,240), the conductive barrier material (240) has a cross-sectional area that is at least twice as large as (or even at least an order of magnitude larger than) that of a conductor layer (140) that provides the electrode connection to the drive element (T1).
9. A device according to any one of the preceding Claims, wherein, along the drive supply line (140,240), the conductive barrier material (240) has a thickness (Z) that is at least twice as large as (or even at least 5 times larger than) that (z) of a conductor layer (140) that provides the electrode connection to the drive element (T1).
10. A device according to any one of the preceding Claims, wherein the physical barriers (210) are predominantly of the conductive barrier material (and preferably comprising metal).
11. A device as claimed in any one of the preceding Claims, wherein the physical barriers (210) extend across the whole array as a continuous supply line of the conductive barrier material (240) that is connected to electrode connections (4,140) for the respective drive elements of the respective pixels.

12. A device according to any one of the preceding Claims, wherein the physical barriers (210) between pixels (200) extend as a network of conductive barrier material (240) in both row and column directions of the array. 5
13. A device according to any one of the preceding Claims, wherein the drive element (T1) is a thin film transistor having source and drain electrodes (3, 4) that connect the main current path of the transistor between the conductive barrier material (240) and a lower electrode (21) of the electroluminescent element (25, LED). 10
14. A device according to any one of the preceding Claims, wherein the drive elements (T1) of the pixels are connected to row and column conductors (150, 160) of the substrate (100) that extend across the array for addressing respective pixels (200), and the supply lines (140,240) comprising the barriers (210) extend parallel to the row and/or column conductors (150, 160). 15 20
15. A device according to any one of the preceding Claims, wherein the drive elements (T1) of the pixels are connected to row and column conductors (150, 160) of the circuit substrate (100) that extend across the array for addressing respective pixels (200), and additional barriers (210c) of conductive material (240) extend parallel to the row conductors (150), are insulated from the barriers (210) that form at least part of the drive supply line (140,240), and are connected at contact windows (12c) in the intermediate insulating layer (12) to the row conductors (150) in the substrate to reduce voltage drops along the row conductors (150). 25 30 35
16. A device according to any one of the preceding Claims, wherein each electroluminescent element (25) comprises a light emitting diode (LED) of organic semiconductor material between upper and lower electrodes (23, 21). 40
17. A method of manufacturing an active matrix electroluminescent display device including the steps of: 45
- (a) opening contact windows (12b) in the intermediate insulating layer (12) on the substrate (100) to expose electrode connections (4,140) for respective drive elements (T1) of at least some of the pixels; 50
 - (b) forming the physical barriers (210) from electrically-conductive material (240) deposited on the insulating layer (12) at least in the contact windows (12b) of the electrode connections; 55
 - (c) providing the electroluminescent elements (25,LED) in the pixel areas in between the physical barriers (210),
- wherein the conductive barrier material is provided by depositing electrically-conductive material at least for connection at the contact windows of the intermediate insulating layer, and **characterised by** further comprising the step of:
- (d) opening contact windows (12a) in the intermediate insulating layer (12) in the pixel areas between the physical barriers, and wherein the electroluminescent elements (25) are provided in the further windows (12a) and have a lower electrode connection (21) to the drive element (T1).
18. A method according to Claim 17, wherein the step (b) involves forming the physical barrier as a core of the electrically-conductive material, and depositing an insulating coating on at least the sides of this conductive barrier material.
19. A method according to claim 18 wherein at least the bulk (240b) of the conductive barrier material (240) is deposited by plating.
20. A method according to Claim 18, wherein the conductive barrier material (240) comprises aluminium, and the insulating coating (40) is formed on at least the sides of the aluminium barrier material by anodisation.
21. A method according to Claim 17, wherein the step (b) involves forming the physical barrier predominantly of insulating material through which vias extend for connection with the circuit element at the contact windows of the intermediate insulating layer, and wherein the electrically-conductive material is deposited as a conductive coating on top of the physical barrier and in the vias through the physical barrier.
22. A method according to Claim 21, wherein the conductive coating for the physical barrier and an upper electrode of the electroluminescent element are deposited simultaneously and are separated by a shadow-masking effect of an overhang shape in the side of the physical barrier.

Patentansprüche

1. Elektrolumineszierende Anzeigevorrichtung mit aktiver Matrix mit einem Substrat (100), auf dem eine Bildpunktmatrix (200) mit physischen Barrieren (210) zwischen benachbarten Bildpunkten in mindestens einer Richtung der Matrix, wobei jeder Bildpunkt (200) ein stromgesteuertes elektrolumineszierendes Bauelement (25, LED) umfasst, das durch ein in Reihe geschaltetes Ansteuerungselement

- (T1) in dem Substrat mit einer Versorgungsleitung (140, 240) verbunden ist, und wobei die physischen Barrieren teilweise aus elektrisch leitendem Material (240) bestehen, das von den elektrolumineszierenden Bauelementen (25, LED) isoliert ist (40) und zumindest einen Teil (240) der Versorgungsleitung (140, 240) bildet, wobei das leitende Barrierematerial (240) mit entsprechenden Ansteuerungselementen (T1) von zumindest einigen der Bildpunkte (200) in Kontaktfenstern (12b) in einer isolierenden Zwischenschicht (12) zwischen den Barrieren (210) und den Ansteuerungselementen (T1) verbunden ist und wobei das elektrolumineszierende Bauelement (25, LED) einen unteren Elektrodenanschluss (21) zum Ansteuerungselement (T1) aufweist, **dadurch gekennzeichnet, dass** das elektrolumineszierende Bauelement (25, LED) in einem weiteren Fenster (12a) in der isolierenden Zwischenschicht vorliegt.
2. Vorrichtung nach Anspruch 1, wobei sich eine isolierende Beschichtung (40) über die Seiten und die Spitze des leitenden Barrierematerials (240) erstreckt und eine weitere Versorgungsleitung (230) obere Elektroden (23) der elektrolumineszierenden Bauelemente (25, LED) umfasst und auf der isolierenden Beschichtung (40) über die Spitze des leitenden Barrierematerials (240) verläuft.
 3. Vorrichtung nach Anspruch 2, wobei die isolierende Beschichtung (40) ein Kondensatordielektrikum eines Glättungskondensators (Cs) zwischen der Ansteuerungsversorgungsleitung (140, 240), die das leitende Barrierematerial umfasst, und der weiteren Versorgungsleitung (230) bildet, die die oberen Elektroden der elektrolumineszierenden Bauelemente umfasst.
 4. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei jeder Bildpunkt (200) ein entsprechendes Kontaktfenster (12b) zwischen dem leitenden Barrierematerial (240) und einem Elektrodenanschluss (4, 140) für das entsprechende Ansteuerungselement (T1) des Bildpunktes aufweist.
 5. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei das Ansteuerungselement (T1) jedes Bildpunktes eine entsprechende Elektrode (4) aufweist, die sich an dem Kontaktfenster (12b) befindet, wo sie mit dem leitenden Barrierematerial (240) verbunden ist.
 6. Vorrichtung nach einem der Ansprüche 1 bis 4, wobei jeder Bildpunkt (200) einen Haltekapazitor (Ch) zum Halten des Ansteuerungselements (T1) in einem gegebenen Leitungszustand umfasst und das leitende Barrierematerial (140) an dem Kontaktfenster (12b) mit einem Knotenpunkt des Ansteuerungselements (T1) und einer Platte des Haltekapazitors (Ch) verbunden ist.
 7. Vorrichtung nach Anspruch 6, wobei die Haltekapazitor durch entsprechende isolierte Längen von zusätzlichen Barrieren (210c) gebildet werden, die quer zu den Versorgungsleitungsbarrieren (201) verlaufen und eine Metallbeschichtung (230) auf einer dielektrischen Beschichtung (40) auf einem Metallkern (240) umfassen.
 8. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei das leitende Barrierematerial (240) entlang der Ansteuerungsversorgungsleitung (140, 240) eine Querschnittsfläche aufweist, die mindestens doppelt so groß wie (oder sogar mindestens eine Größenordnung größer als) diejenige einer Leiterschicht (140) ist, die den Elektrodenanschluss zum Ansteuerungselement (T1) bildet.
 9. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei das leitende Barrierematerial (240) entlang der Ansteuerungsversorgungsleitung (140, 240) eine Dicke (Z) hat, die mindestens doppelt so groß (oder sogar mindestens fünfmal so groß) wie diejenige (z) einer Leiterschicht (140) ist, die den Elektrodenanschluss zum Ansteuerungselement (T1) schafft.
 10. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei die physischen Barrieren (210) vorwiegend aus dem leitenden Barrierematerial (und vorzugsweise mit Metall) bestehen.
 11. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei die physischen Barrieren (210) über die gesamte Matrix als eine durchgehende Versorgungsleitung aus dem leitenden Barrierematerial (240) verlaufen, die mit den Elektrodenanschlüssen (4, 140) für die entsprechenden Ansteuerungselemente der entsprechenden Bildpunkte verbunden ist.
 12. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei die physischen Barrieren (210) zwischen den Bildpunkten (200) wie ein Netz aus leitendem Barrierematerial (240) sowohl in Zeilen- als auch in Spaltenrichtung der Matrix verlaufen.
 13. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei das Ansteuerungselement (T1) ein Dünnschichttransistor mit Source- und Drain-Elektroden (3, 4) ist, die den Hauptstrompfad des Transistors zwischen dem leitenden Barrierematerial (240) und einer unteren Elektrode (21) des elektrolumineszierenden Bauelements (25, LED) verbinden.

14. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei die Ansteuerungselemente (T1) der Bildpunkte mit den Zeilen- und Spaltenleitungen (150, 160) des Substrats (100) verbunden sind, die zur Adressierung der entsprechenden Bildpunkte (200) über die Matrix verlaufen, und wobei die Versorgungsleitungen (140, 240) mit den Barrieren (210) parallel zu den Zeilen- und/oder Spaltenleitungen (150, 160) verlaufen.

15. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei die Ansteuerungselemente (T1) der Bildpunkte mit den Zeilen- und Spaltenleitungen (150, 160) des Substrats (100) verbunden sind, die zur Adressierung der entsprechenden Bildpunkte (200) über die Matrix verlaufen, und wobei zusätzliche Barrieren (210c) aus leitendem Material (240) parallel zu den Zeilenleitungen (150) verlaufen, von den Barrieren (210) isoliert sind, die zumindest einen Teil der Ansteuerungsversorgungsleitung (140, 240) bilden, und an den Kontaktfenstern (12c) in der isolierenden Zwischenschicht (12) mit den Zeilenleitungen (150) in dem Substrat verbunden sind, um Spannungsabfälle entlang der Zeilenleitungen (150) zu reduzieren.

16. Vorrichtung nach einem der vorhergehenden Ansprüche, wobei jedes elektrolumineszierende Bauelement (25) eine Leuchtdiode (LED) aus organischem Halbleitermaterial zwischen den oberen und unteren Elektroden (23, 21) umfasst.

17. Verfahren zur Herstellung einer elektrolumineszierenden Anzeigevorrichtung mit aktiver Matrix, das die folgenden Schritte umfasst:

(a) Öffnen von Kontaktfenstern (12b) in der isolierenden Zwischenschicht (12) auf dem Substrat (100) zum Freilegen von Elektrodenanschlüssen (4, 140) für die entsprechenden Ansteuerungselemente (T1) von zumindest einigen der Bildpunkte,

(b) Bilden von physischen Barrieren (210) aus elektrisch leitendem Material (240), das auf der isolierenden Schicht (12) zumindest in den Kontaktfenstern (12b) der Elektrodenanschlüsse abgeschieden wird,

(c) Schaffen von elektrolumineszierenden Bauelementen (25, LED) in den Bildpunktbereichen zwischen den physischen Barrieren (210), wobei das leitende Barrierematerial durch Abscheiden von elektrisch leitendem Material zumindest für den Anschluss an den Kontaktfenstern der isolierenden Zwischenschicht gebildet wird,

und **dadurch gekennzeichnet, dass** es ferner den folgenden Schritt umfasst:

(d) Öffnen von Kontaktfenstern (12a) in der iso-

lierenden Zwischenschicht (12) in den Bildpunktbereichen zwischen den physischen Barrieren, und wobei die elektrolumineszierenden Bauelemente (25) in den zusätzlichen Fenstern (12a) geschaffen werden und einen unteren Elektrodenanschluss (21) zu dem Ansteuerungselement (T1) aufweisen.

18. Verfahren nach Anspruch 17, wobei der Schritt (b) das Bilden der physischen Barriere als Kern des elektrisch leitenden Materials und das Abscheiden einer isolierenden Beschichtung auf zumindest den Seiten dieses leitenden Barrierematerials beinhaltet.

19. Verfahren nach Anspruch 18, wobei zumindest der Großteil (240b) des leitenden Barrierematerials (240) durch Plattieren abgeschieden wird.

20. Verfahren nach Anspruch 18, wobei das leitende Barrierematerial (240) Aluminium enthält und die isolierende Beschichtung (40) zumindest auf den Seiten des Aluminium-Barrierematerials durch Anodisieren gebildet wird.

21. Verfahren nach Anspruch 17, wobei der Schritt (b) das Bilden der physischen Barriere vorwiegend aus isolierendem Material beinhaltet, durch das Durchkontaktierungen zum Anschluss des Schaltungselements an den Kontaktfestern der isolierenden Zwischenschicht verlaufen, und wobei das elektrisch leitende Material als leitende Beschichtung oben auf der physischen Barriere und in den Durchkontaktierungen durch die physische Barriere abgeschieden wird.

22. Verfahren nach Anspruch 21, wobei die leitende Beschichtung für die physische Barriere und die obere Elektrode des elektrolumineszierenden Bauelements gleichzeitig abgeschieden werden und durch den Lochmaskeneffekt einer überhängenden Form in der Seite der physischen Barriere getrennt werden.

Revendications

1. Dispositif d'affichage électroluminescent à matrice active comprenant un substrat (100) sur lequel se trouve une matrice de pixels (200) avec des barrières physiques (210) entre des pixels voisins dans au moins une direction de la matrice, dans lequel chaque pixel (200) comprend un élément électroluminescent activé par un courant (25 ; LED) qui est relié à une ligne d'alimentation (140, 240) par un élément d'activation en série (T1) dans le substrat, et dans lequel les barrières physiques sont partiellement constituées d'un matériau conducteur d'électricité

(240) qui est isolé (40) des éléments électroluminescents (25 ; LED) et qui fournit au moins une partie (240) de la ligne d'alimentation (140, 240), ledit matériau barrière conducteur (240) étant relié aux éléments d'activation respectifs (T1) d'au moins une partie des pixels (200) dans des fenêtres de contact (12b) d'une couche isolante intermédiaire (12) entre les barrières (210) et les éléments d'activation (T1), et dans lequel l'élément électroluminescent (25, LED) a une liaison d'électrode inférieure (21) avec l'élément d'activation (T1),
caractérisé en ce que l'élément électroluminescent (25, LED) se trouve dans une autre fenêtre (12a) de la couche isolante intermédiaire (12).

2. Dispositif selon la revendication 1, dans lequel un revêtement isolant (40) s'étend sur les côtés et sur la partie supérieure du matériau barrière conducteur (240), et une autre ligne d'alimentation (230) comprend des électrodes supérieures (23) des éléments électroluminescents (25 ; LED) et s'étend sur le revêtement isolant (40) sur la partie supérieure du matériau barrière conducteur (240).
3. Dispositif selon la revendication 2, dans lequel le revêtement isolant (40) forme un diélectrique de condensateur d'un condensateur de filtrage (Cs) entre la ligne d'alimentation d'activation (140, 240) qui comprend le matériau barrière conducteur et l'autre ligne d'alimentation (230) qui comprend les électrodes supérieures des éléments électroluminescents.
4. Dispositif selon l'une quelconque des revendications précédentes, dans lequel chaque pixel (200) possède une fenêtre de contact respective (12b) entre le matériau barrière conducteur (240) et une liaison d'électrode (4, 140) pour l'élément d'activation respectif (T1) du pixel.
5. Dispositif selon l'une quelconque des revendications précédentes, dans lequel l'élément d'activation (T1) de chaque pixel possède une électrode respective (4) située dans la fenêtre de contact (12b) où il est relié au matériau barrière conducteur (240).
6. Dispositif selon l'une quelconque des revendications 1 à 4, dans lequel chaque pixel (200) comprend un condensateur de maintien (Ch) destiné à maintenir l'élément d'activation (T1) dans un état de conduction donné, et le matériau barrière conducteur (140) est relié dans la fenêtre de contact (12b) à un noeud de l'élément d'activation (T1) et à une plaque du condensateur de maintien (Ch).
7. Dispositif selon la revendication 6, dans lequel les condensateurs de maintien sont formés par des longueurs isolées respectives de barrières supplémentaires (210c) qui s'étendent perpendiculairement

aux barrières de lignes d'alimentation (210) et qui comprennent un revêtement métallique (230) appliqué sur un revêtement diélectrique (40) appliqué sur un noyau métallique (240).

8. Dispositif selon l'une quelconque des revendications précédentes dans lequel, le long de la ligne d'alimentation d'activation (140, 240), le matériau barrière conducteur (240) a une surface de section transversale qui est au moins deux fois supérieure (voire supérieure d'au moins un ordre de grandeur) à celle d'une couche conductrice (140) qui fournit la liaison d'électrode avec l'élément d'activation (T1).
9. Dispositif selon l'une quelconque des revendications précédentes dans lequel, le long de la ligne d'alimentation d'activation (140, 240), le matériau barrière conducteur (240) a une épaisseur (Z) qui est au moins deux fois supérieure (voire au moins 5 fois supérieure) à celle (z) d'une couche conductrice (140) qui fournit la liaison d'électrode avec l'élément d'activation (T1).
10. Dispositif selon l'une quelconque des revendications précédentes, dans lequel les barrières physiques (210) sont principalement constituées du matériau barrière conducteur (et comprenant de préférence un métal).
11. Dispositif selon l'une quelconque des revendications précédentes, dans lequel les barrières physiques (210) s'étendent à travers l'ensemble de la matrice sous forme d'une ligne d'alimentation continue du matériau barrière conducteur (240) qui est connectée aux liaisons d'électrode (4, 140) pour les éléments d'activation respectifs des pixels respectifs.
12. Dispositif selon l'une quelconque des revendications précédentes, dans lequel les barrières physiques (210) entre les pixels (200) s'étendent sous la forme d'un réseau de matériau barrière conducteur (240) dans le sens des lignes et dans le sens des colonnes de la matrice.
13. Dispositif selon l'une quelconque des revendications précédentes, dans lequel l'élément d'activation (T1) est un transistor à couche mince ayant des électrodes de source et de drain (3, 4) qui relient le trajet de courant principal du transistor entre le matériau barrière conducteur (240) et une électrode inférieure (21) de l'élément électroluminescent (25, LED).
14. Dispositif selon l'une quelconque des revendications précédentes, dans lequel les éléments d'activation (T1) des pixels sont reliés à des conducteurs de ligne et de colonne (150, 160) du substrat (100) qui s'étendent à travers la matrice pour attaquer des pixels respectifs (200), et les lignes d'alimentation (140,

240) comprenant les barrières (210) s'étendent parallèlement aux conducteurs de ligne et/ou de colonne (150, 160).

15. Dispositif selon l'une quelconque des revendications précédentes, dans lequel les éléments d'activation (T1) des pixels sont reliés à des conducteurs de ligne et de colonne (150, 160) du substrat de circuit (100) qui s'étendent à travers la matrice pour attaquer des pixels respectifs (200), et des barrières supplémentaires (210c) d'un matériau conducteur (240) s'étendent parallèlement aux conducteurs de ligne (150), sont isolés des barrières (210) qui forment au moins une partie de la ligne d'alimentation d'activation (140, 240), et sont reliés dans des fenêtres de contact (12c) de la couche isolante intermédiaire (12) aux conducteurs de ligne (150) du substrat pour limiter les chutes de tension le long des conducteurs de ligne (150). 5
16. Dispositif selon l'une quelconque des revendications précédentes, dans lequel chaque élément électroluminescent (25) comprend une diode électroluminescente (DEL) d'un matériau semi-conducteur organique entre des électrodes supérieure et inférieure (23, 21). 10
17. Procédé de fabrication d'un dispositif d'affichage électroluminescent à matrice active, comprenant les étapes qui consistent à : 15
 - (a) ouvrir des fenêtres de contact (12b) dans la couche isolante intermédiaire (12) du substrat (100) pour exposer les liaisons d'électrode (4, 140) des éléments d'activation respectifs (T1) d'au moins une partie des pixels ; 20
 - (b) former les barrières physiques (210) à partir d'un matériau conducteur d'électricité (240) déposé sur la couche isolante (12) au moins dans les fenêtres de contact (12b) des liaisons d'électrode ; 25
 - (c) fournir les éléments électroluminescents (25, LED) dans les zones de pixels entre les barrières physiques (210), dans lequel le matériau barrière conducteur est fourni par dépôt d'un matériau conducteur d'électricité au moins pour la liaison dans les fenêtres de contact de la couche isolante intermédiaire, et **caractérisé en ce qu'il** comprend en outre l'étape consistant à : 30
 - (d) ouvrir des fenêtres de contact (12a) dans la couche isolante intermédiaire (12) dans les zones de pixels situées entre les barrières physiques, et dans lequel les éléments électroluminescents (25) sont fournis dans les autres fenêtres (12a) et ont une liaison d'électrode inférieure (21) avec l'élément d'activation (T1). 35

18. Procédé selon la revendication 17, dans lequel l'étape (b) consiste à former la barrière physique en tant que noyau du matériau conducteur d'électricité, et à déposer un revêtement isolant sur au moins les côtés de ce matériau barrière conducteur. 40
19. Procédé selon la revendication 18, dans lequel au moins la plus grande partie (240b) du matériau barrière conducteur (240) est déposée par placage. 45
20. Procédé selon la revendication 18, dans lequel le matériau barrière conducteur (240) comprend de l'aluminium, et le revêtement isolant (40) est formé sur au moins les côtés de la barrière d'aluminium par anodisation. 50
21. Procédé selon la revendication 17, dans lequel l'étape (b) consiste à former la barrière physique principalement d'un matériau isolant à travers s'étendent lequel des trous d'interconnexion destinés à la liaison avec l'élément de circuit dans les fenêtres de contact de la couche isolante intermédiaire, et dans lequel le matériau conducteur d'électricité est déposé sous la forme d'un revêtement conducteur sur la partie supérieure de la barrière physique et dans les trous d'interconnexion à travers la barrière physique. 55
22. Procédé selon la revendication 21, dans lequel le revêtement conducteur de la barrière physique et une électrode supérieure de l'élément électroluminescent sont déposés simultanément et sont séparés par un effet de masque perforé en surplomb dans le côté de la barrière physique.

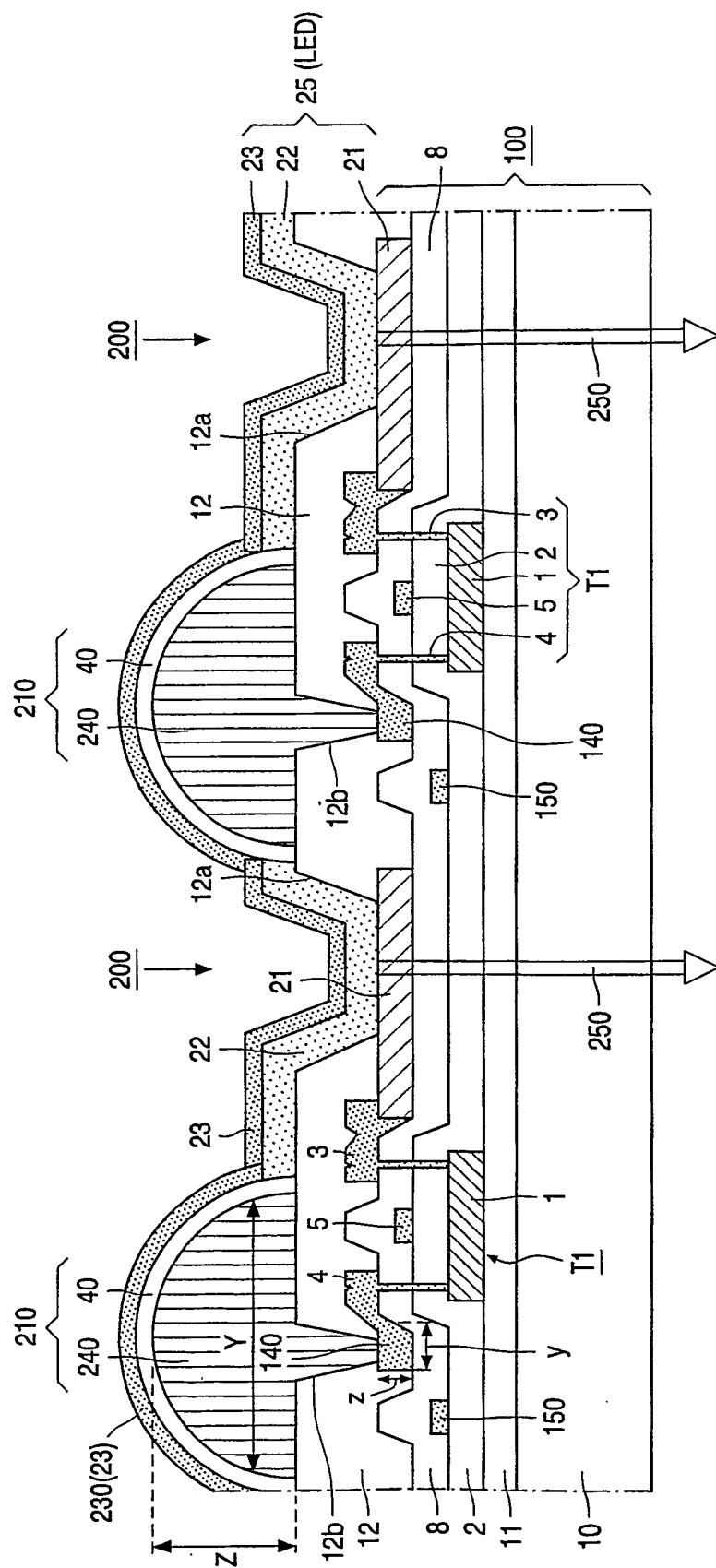


FIG. 1

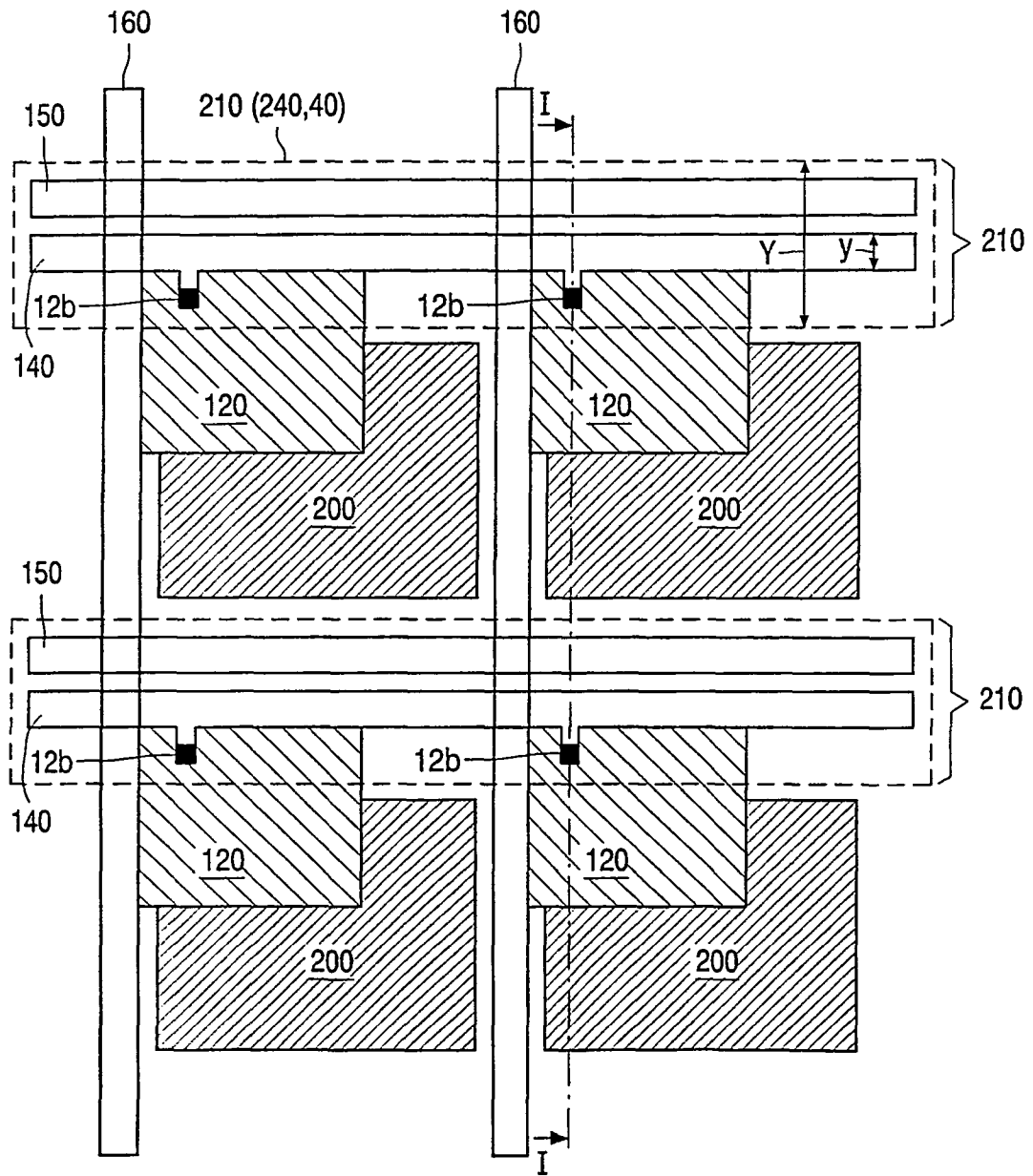


FIG. 2

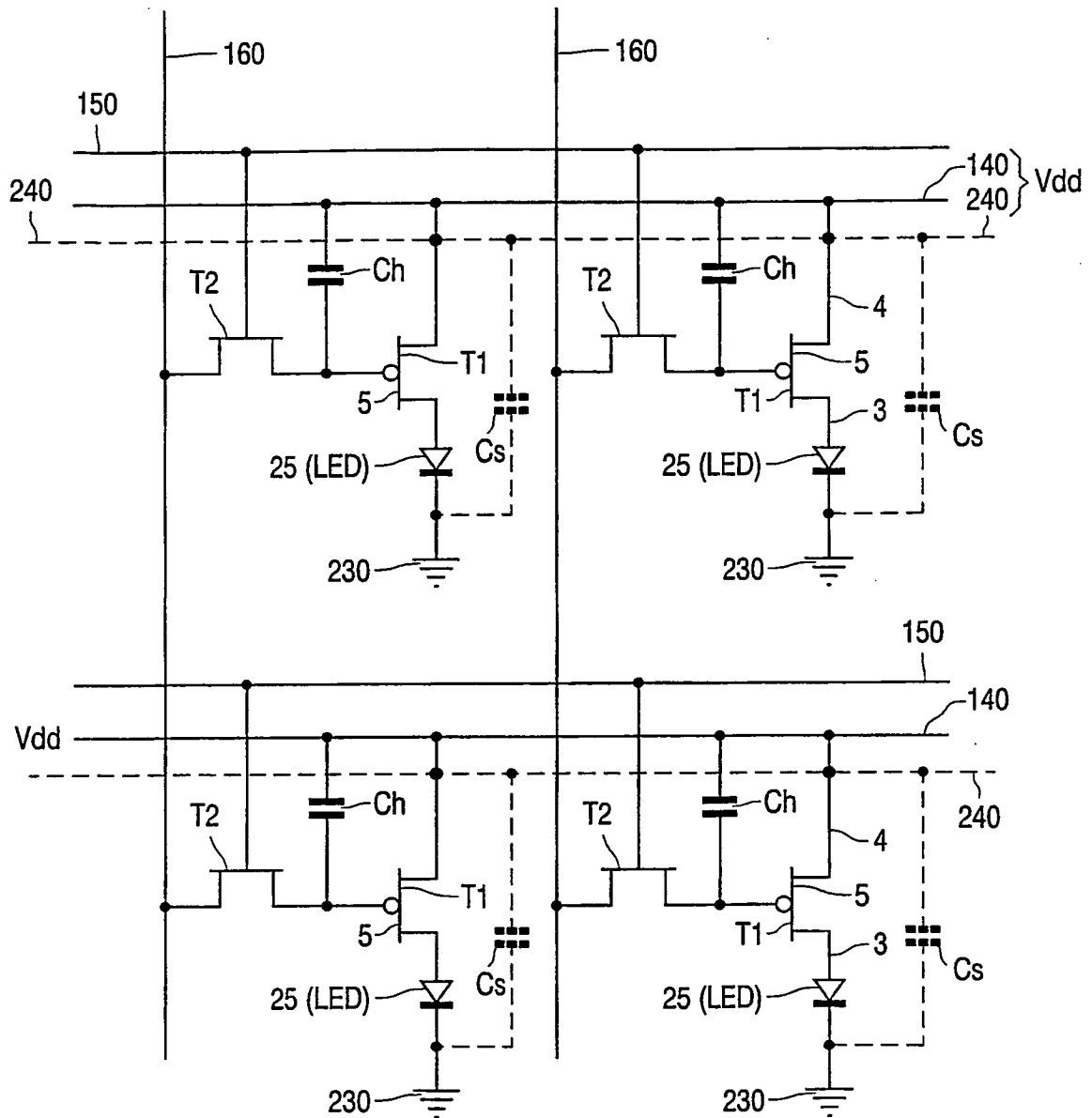


FIG. 3

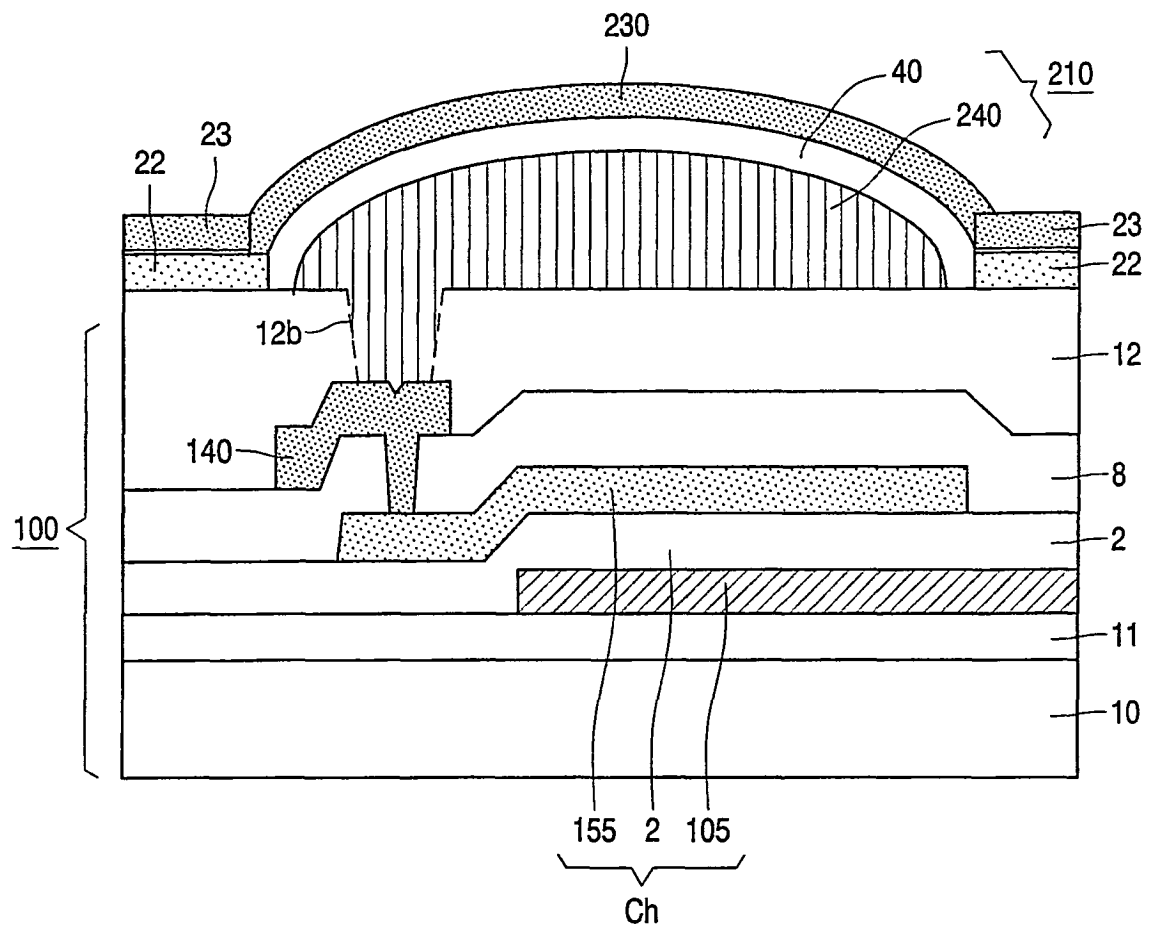


FIG. 4

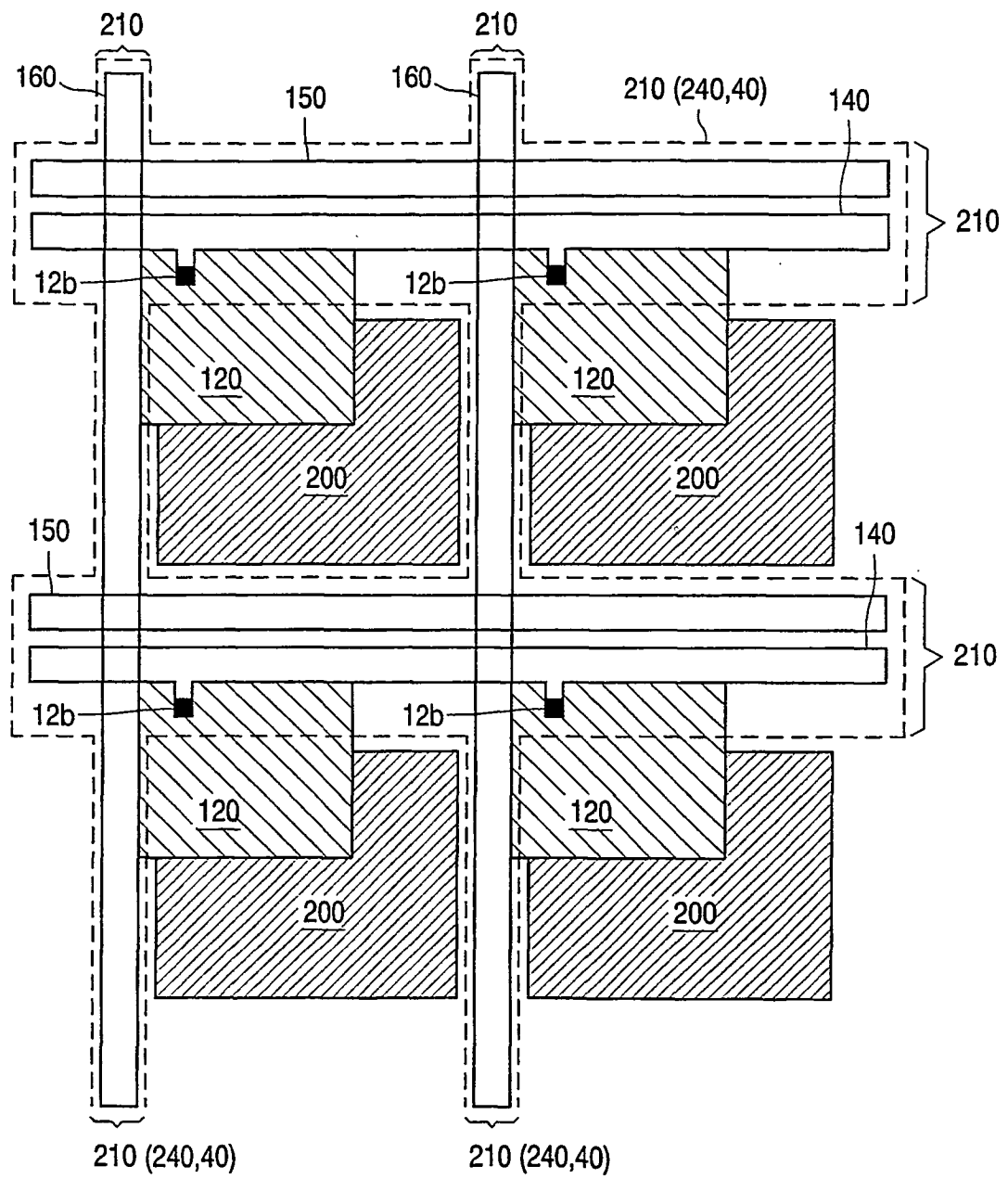


FIG. 5

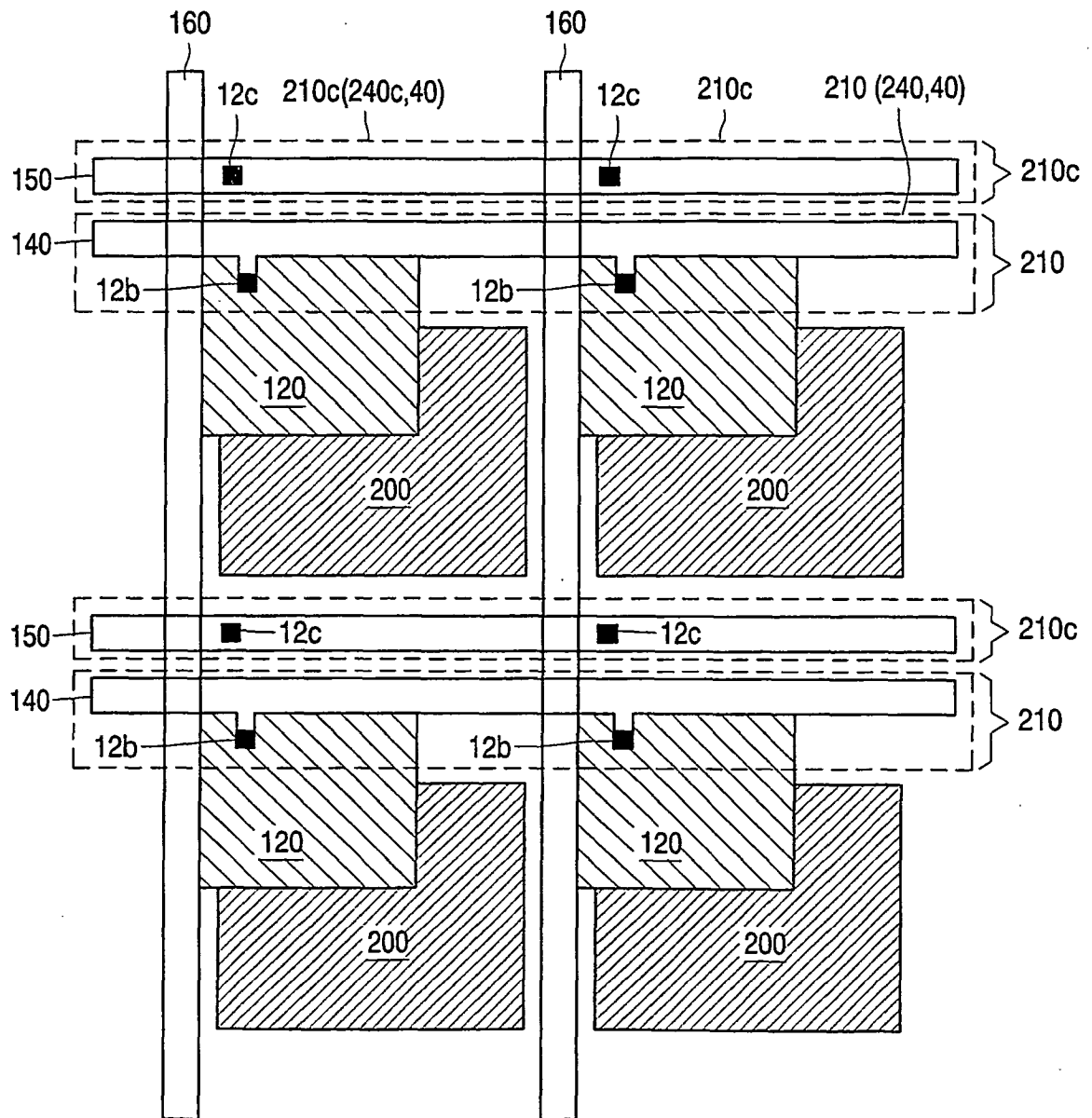


FIG. 6

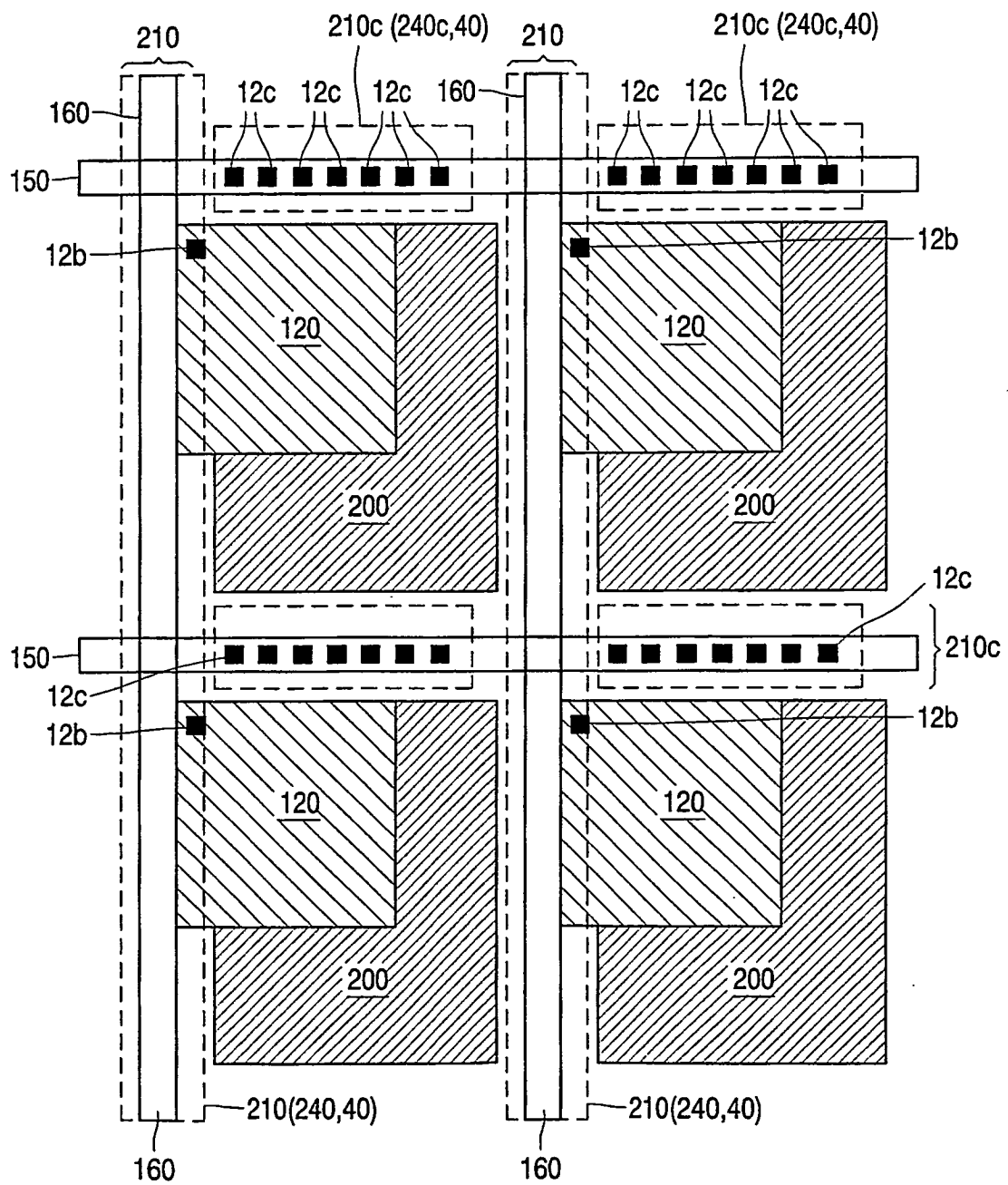


FIG. 7

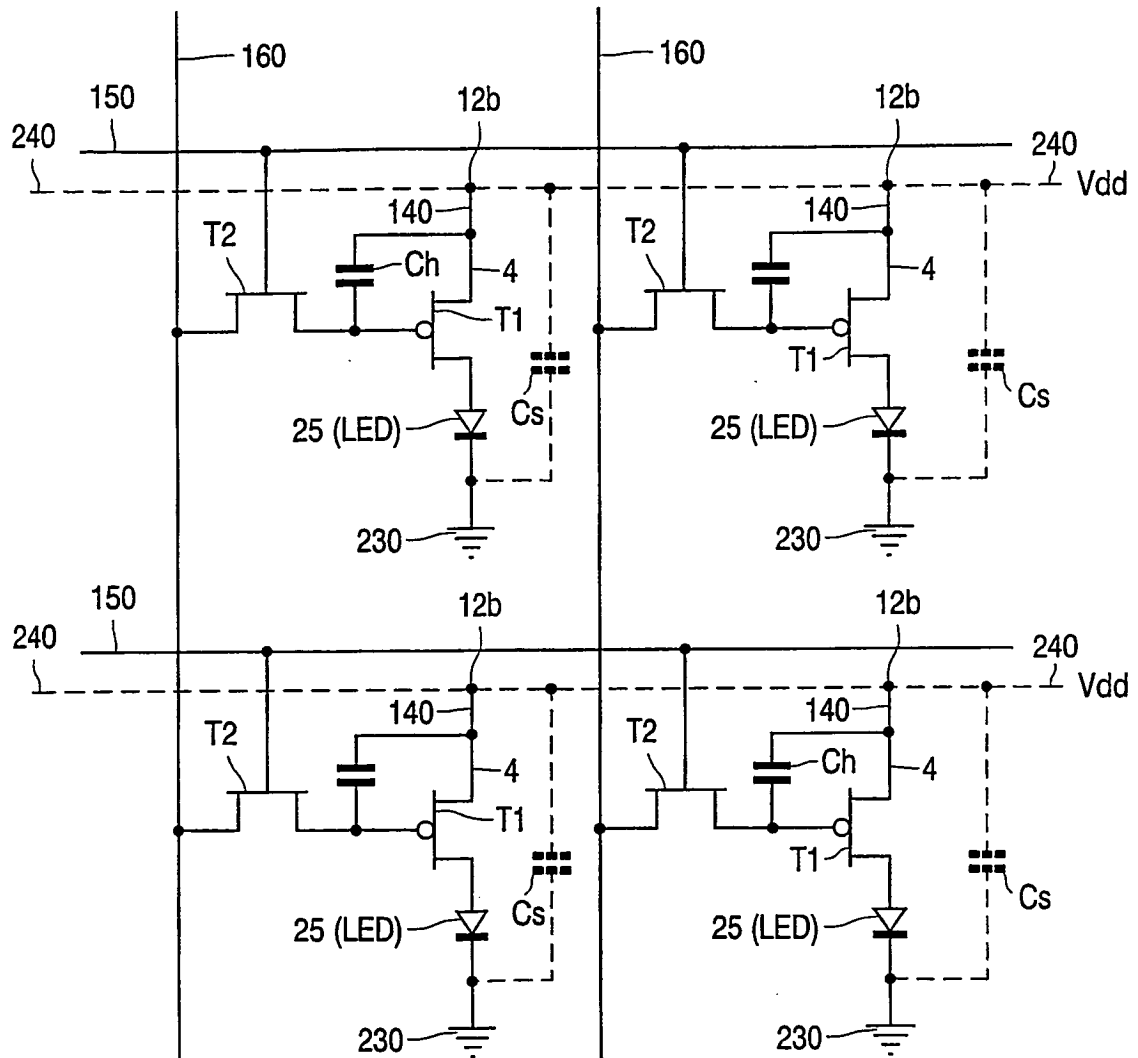


FIG. 8

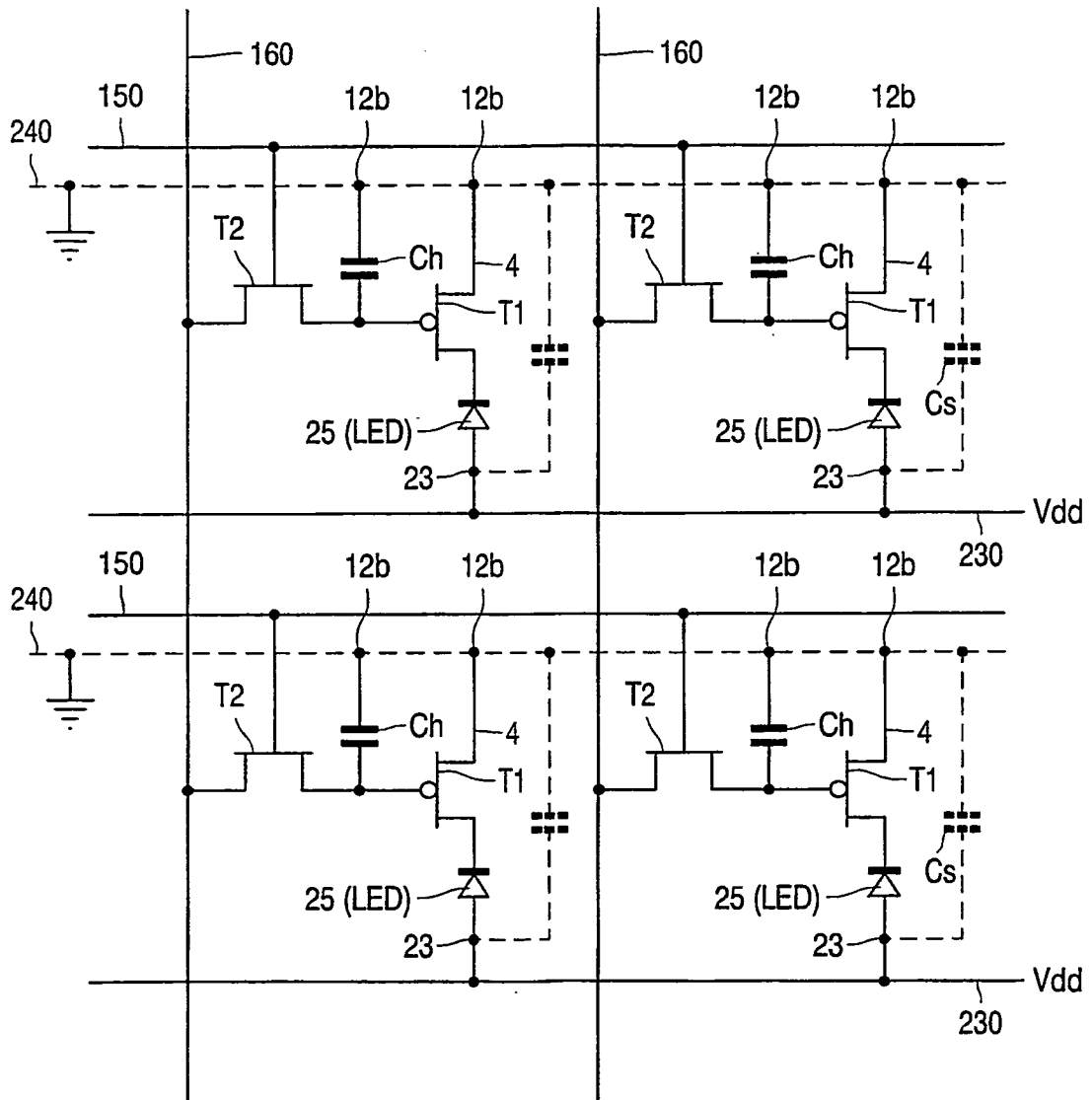


FIG. 9

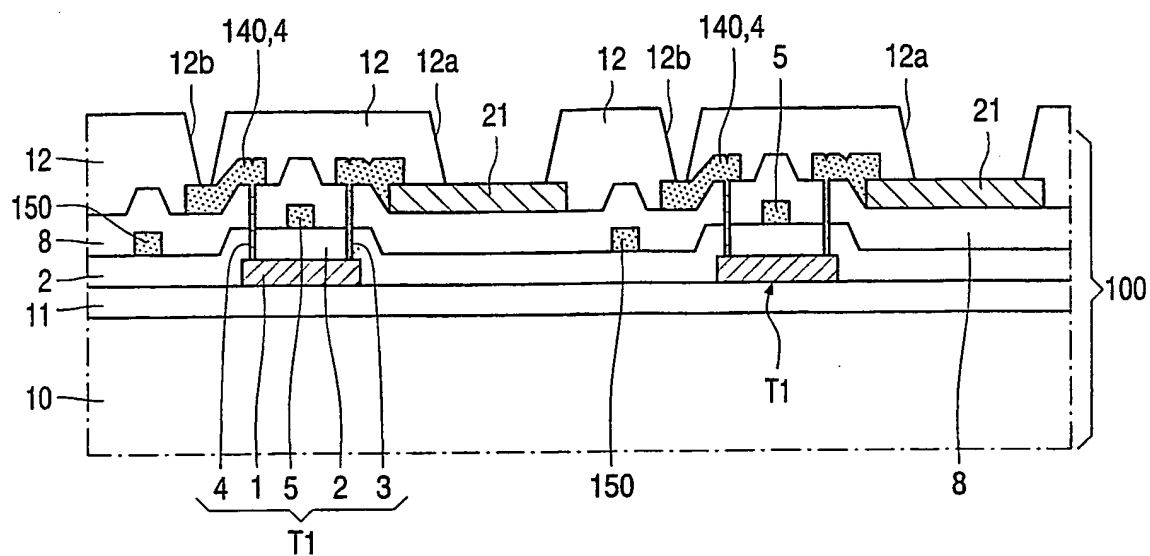


FIG. 10

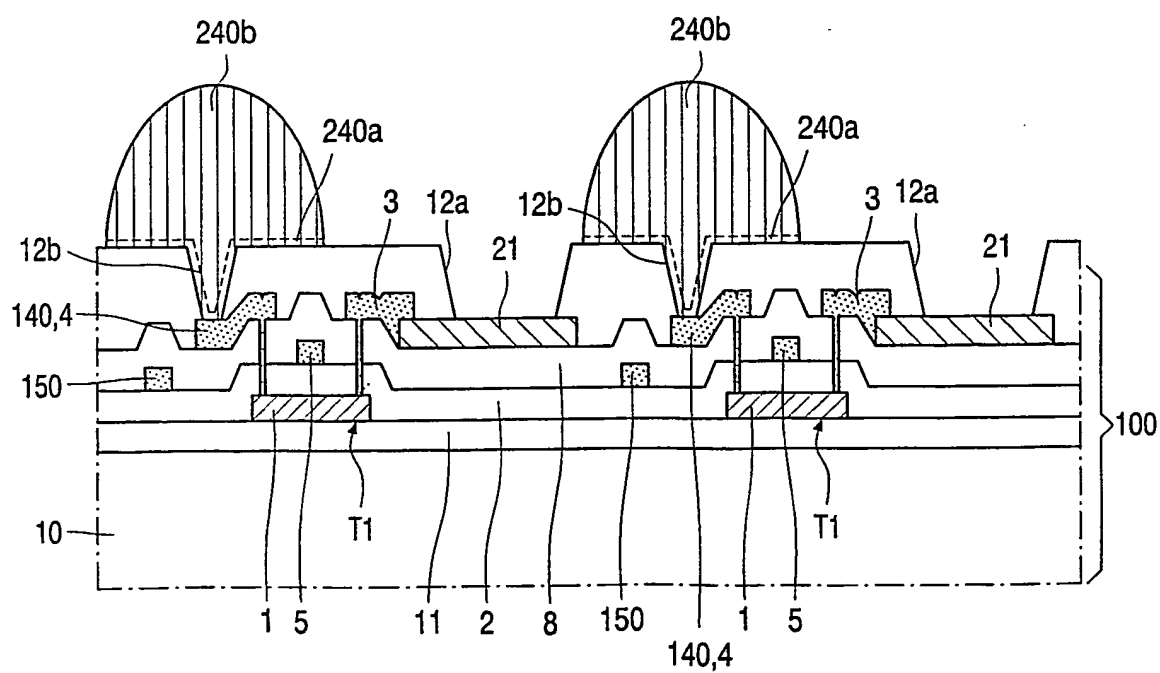


FIG. 11

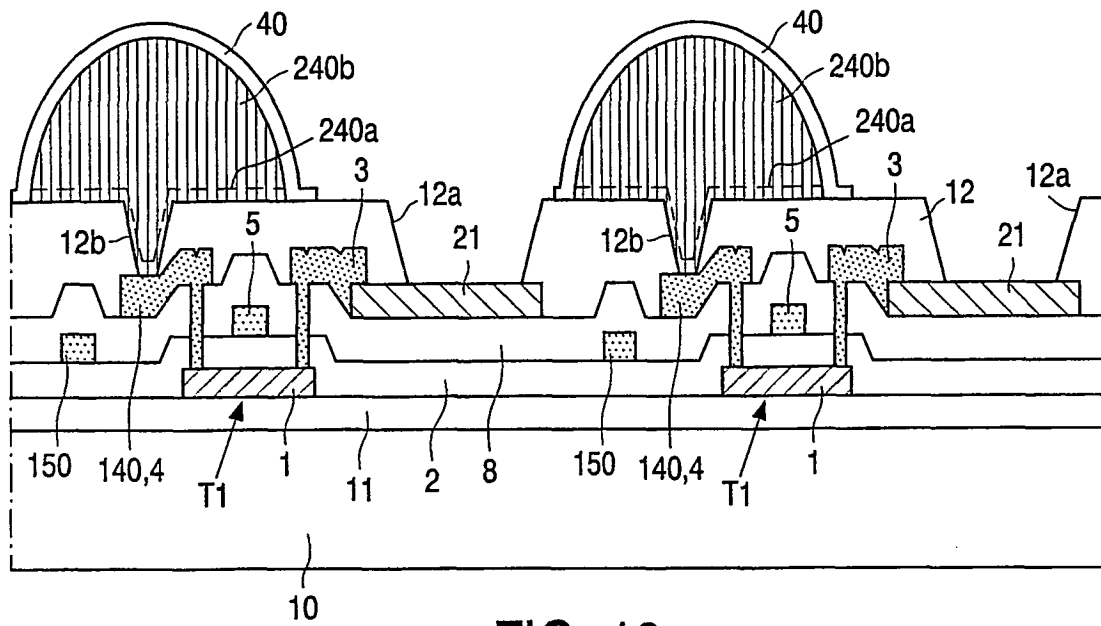


FIG. 12

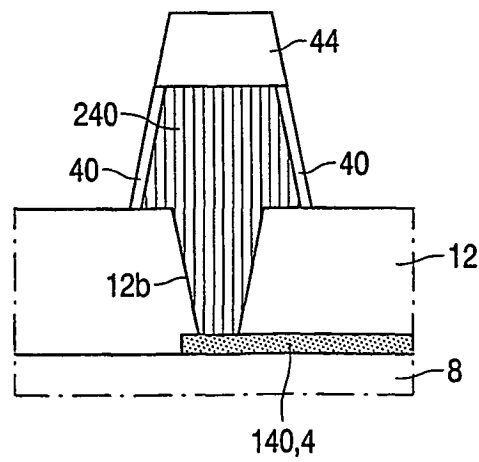


FIG. 13

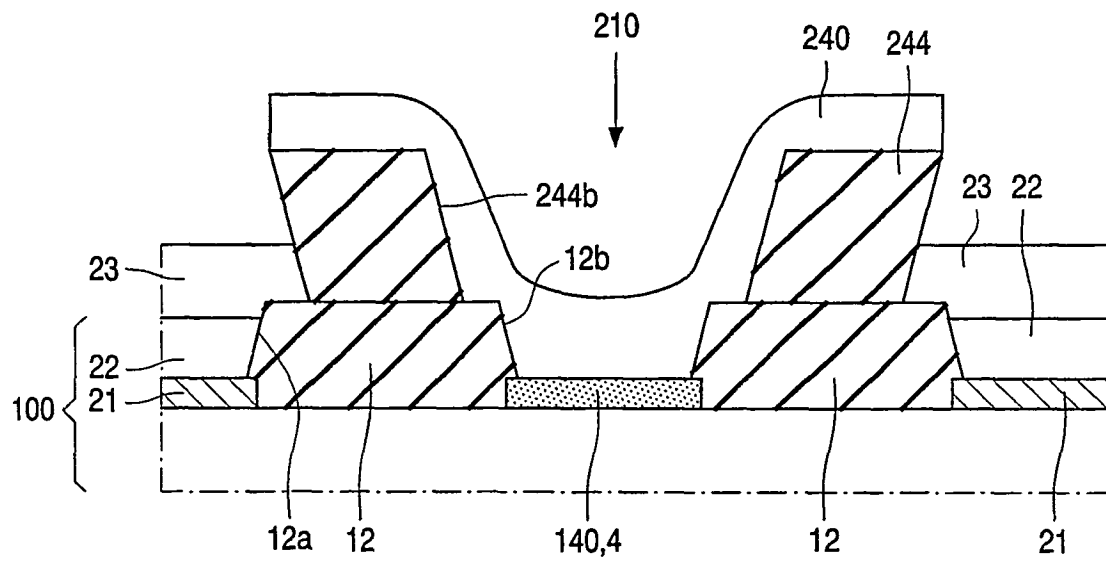


FIG. 14

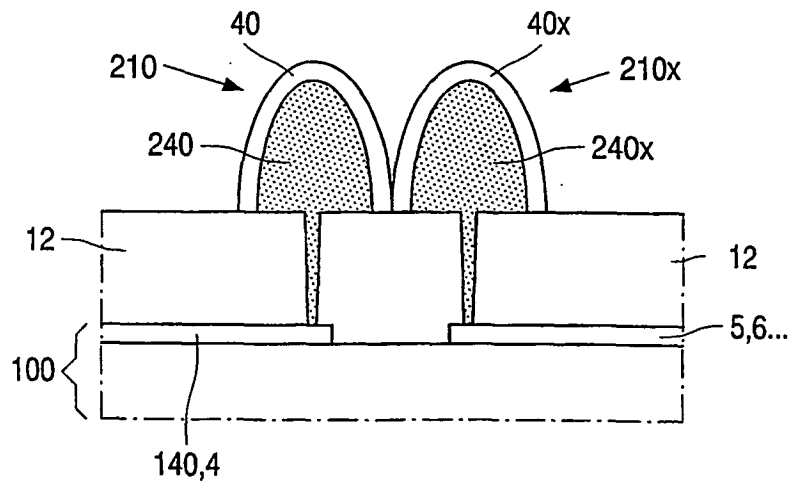


FIG. 15

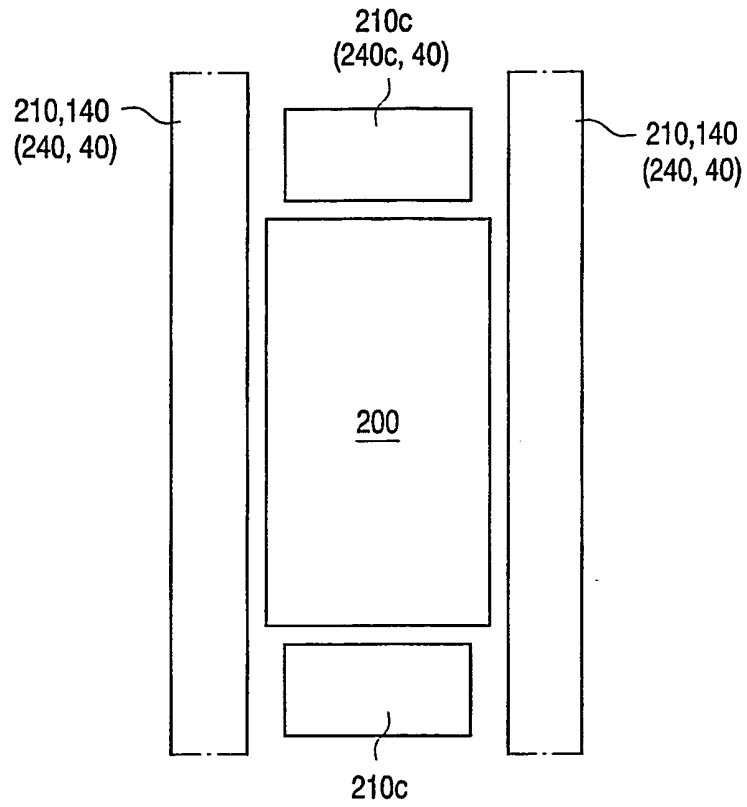


FIG. 16

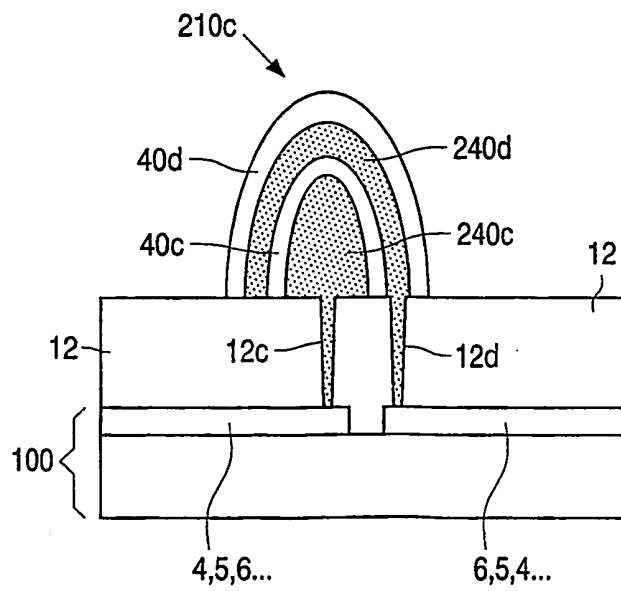


FIG. 17

REFERENCES CITED IN THE DESCRIPTION

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摘要(译)

物理屏障(210)存在于有源矩阵电致发光显示装置的电路板(100)上的相邻像素(200)之间,特别是有机半导体材料的LED(25)。本发明利用金属或其他导电材料(240)形成这些屏障(210),其与LED绝缘(40)但连接到基板(100)内的电路。该导电阻挡材料(240)通过驱动元件T1备份或替换LED连接到的驱动供应线(140,240)的至少一部分。这将线路电阻和相关电压降的问题从电路板(100)内严格限制,转移到基板(100)上的像素屏障(210)的更自由的环境中,其中导电屏障材料(240)可以提供更低的阻力。可以使用该复合驱动电源线(140,240)的低压降制作非常大的显示器。此外,可以优化该结构以在该驱动电源线(140,240)与其导电阻挡材料(240)之间形成平滑电容器(Cs),并且LED上电极(23)的另一电源线(230)在其上延伸。绝缘涂层(40)位于导电阻挡材料(240)的顶部上方。

